

Topological Band and Correlated Insulators

Part 2

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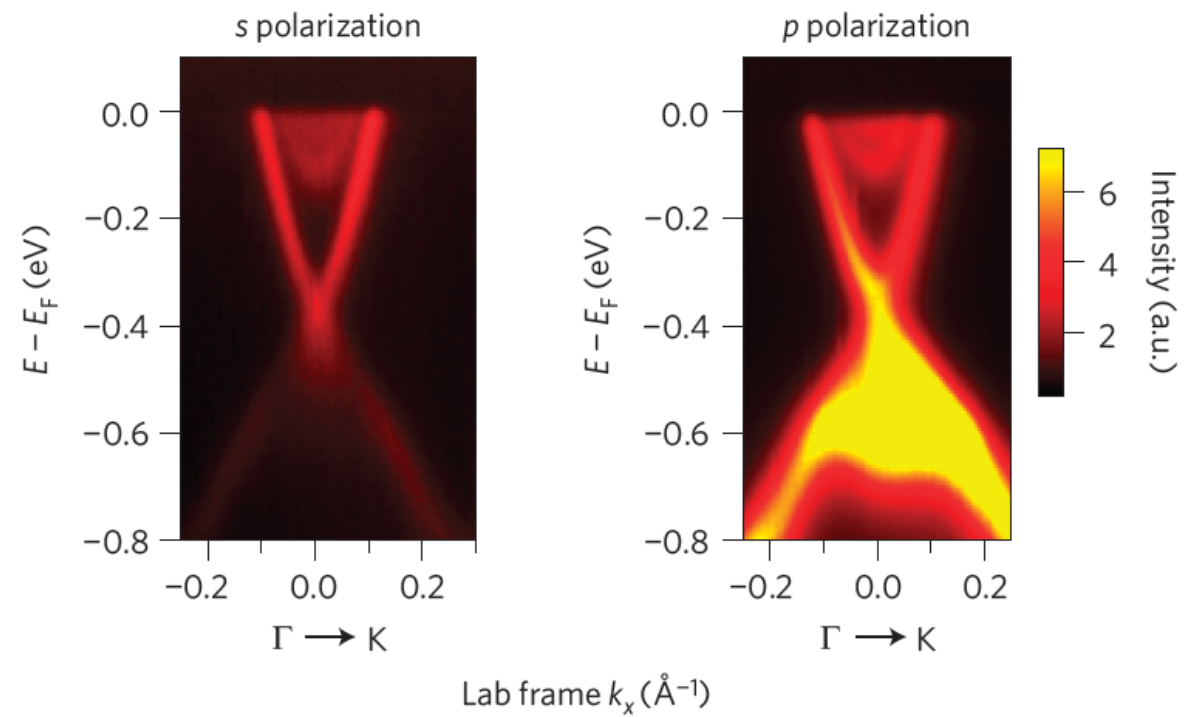
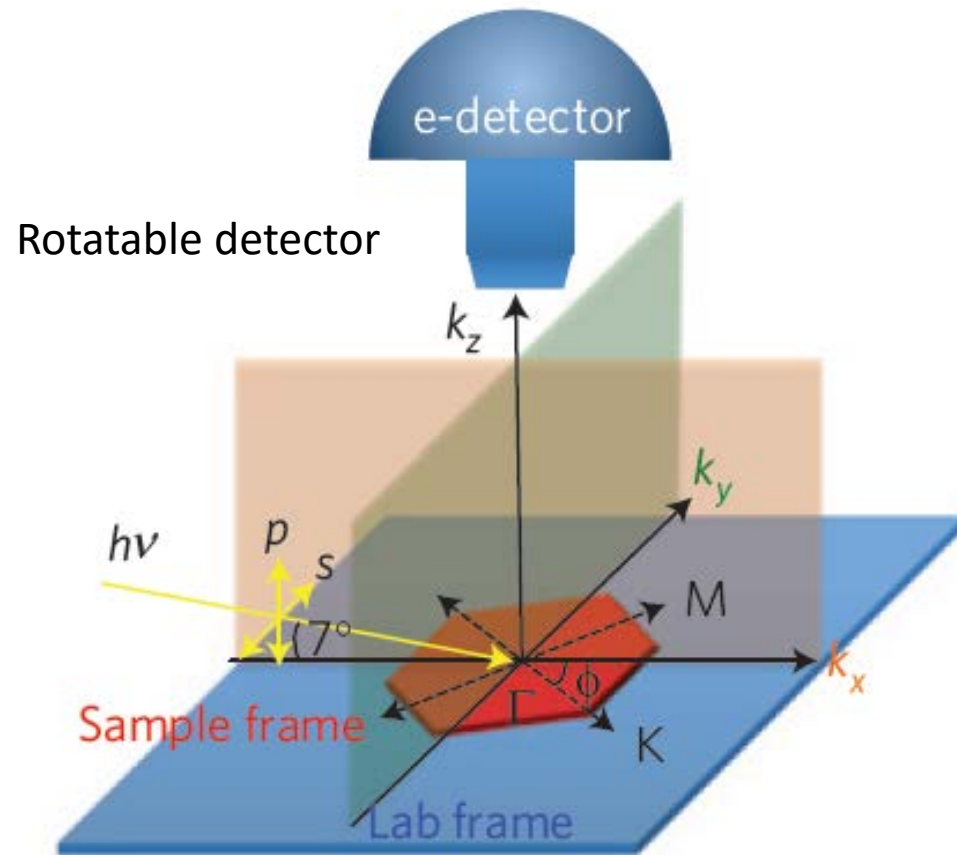
Caltech

IQIM

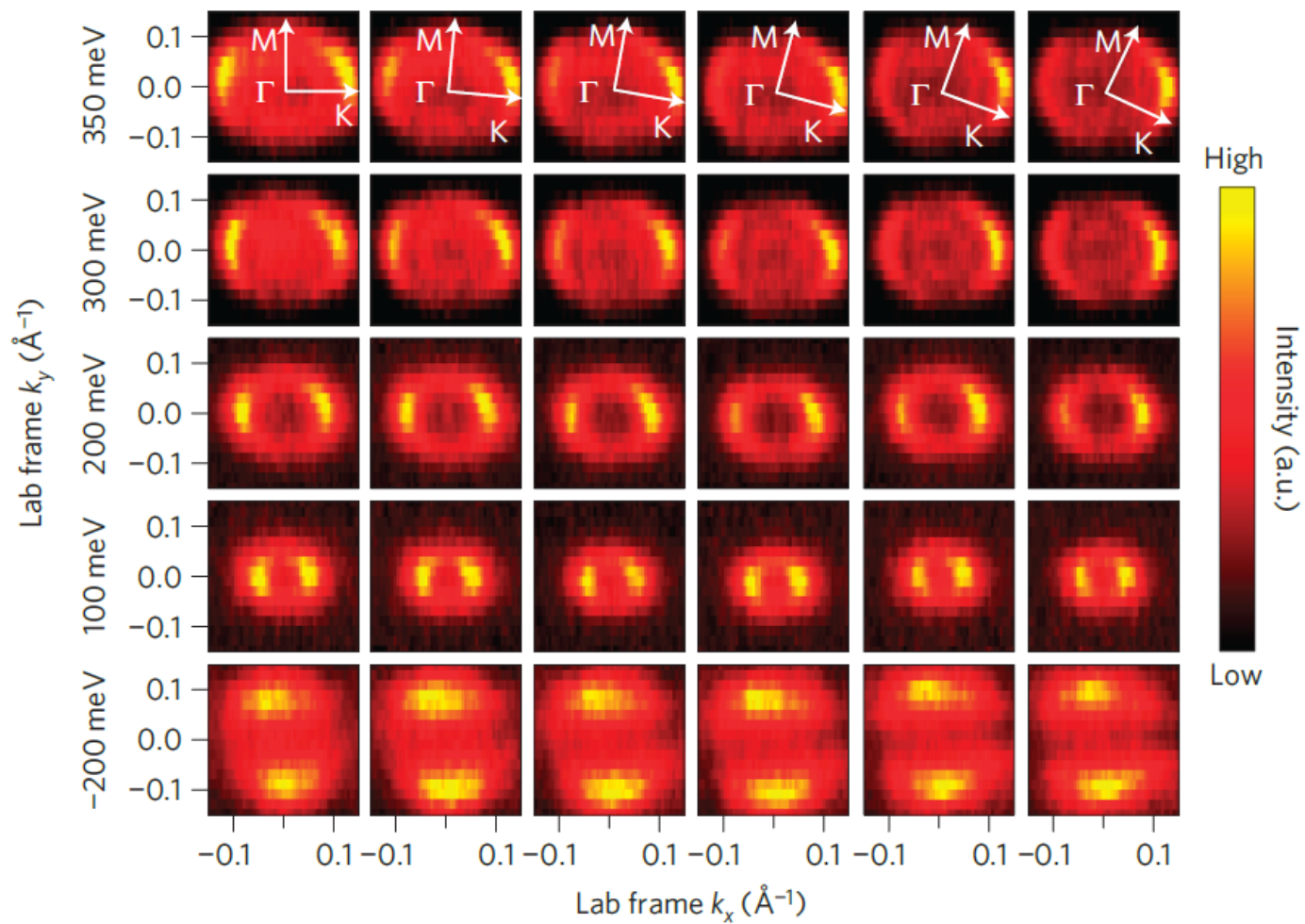
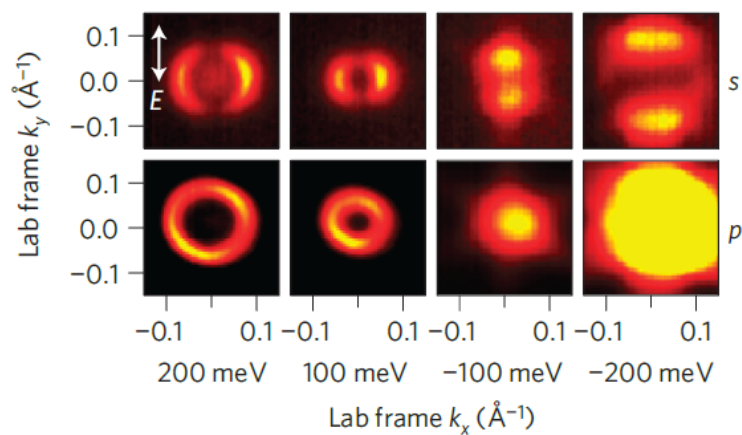
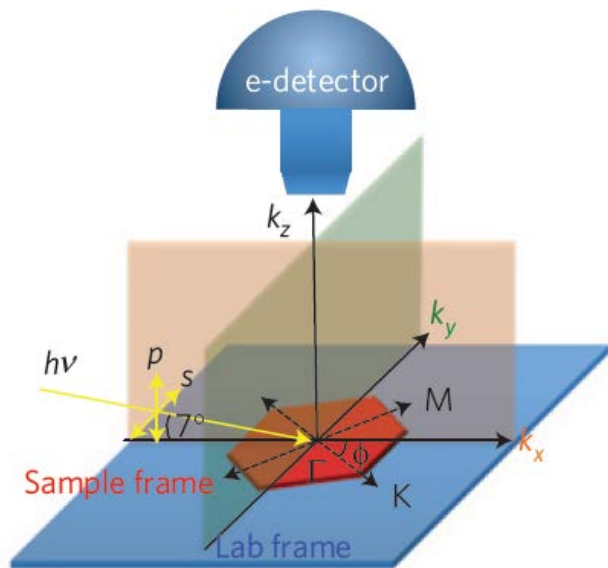
Outline

- Orbital texture of topological surface states
- Correlated topological insulators
 - Heavy transition metal oxides
 - *f*-electron heavy fermion systems
- Superconducting topological insulators

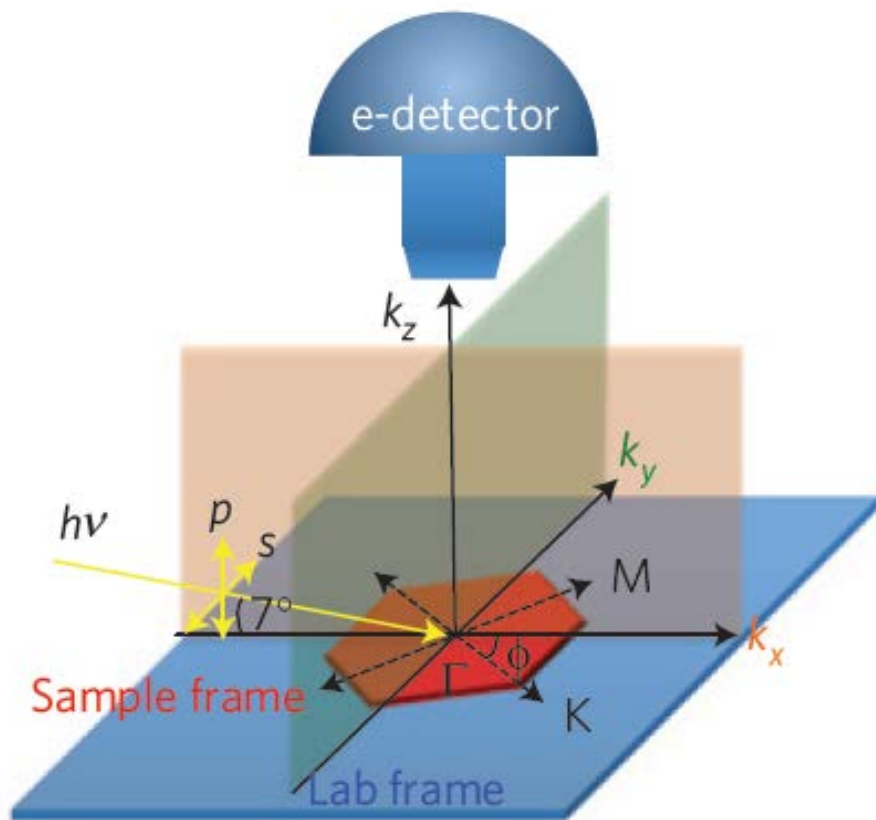
Orbital texture



Orbital texture

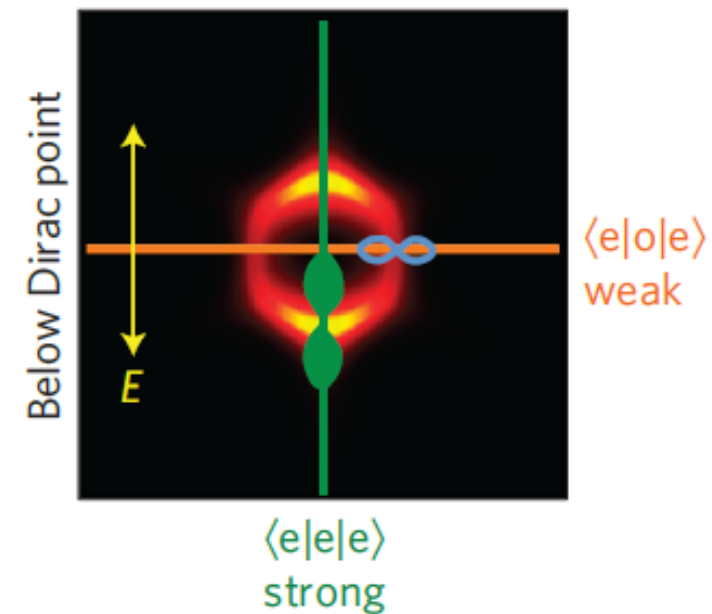
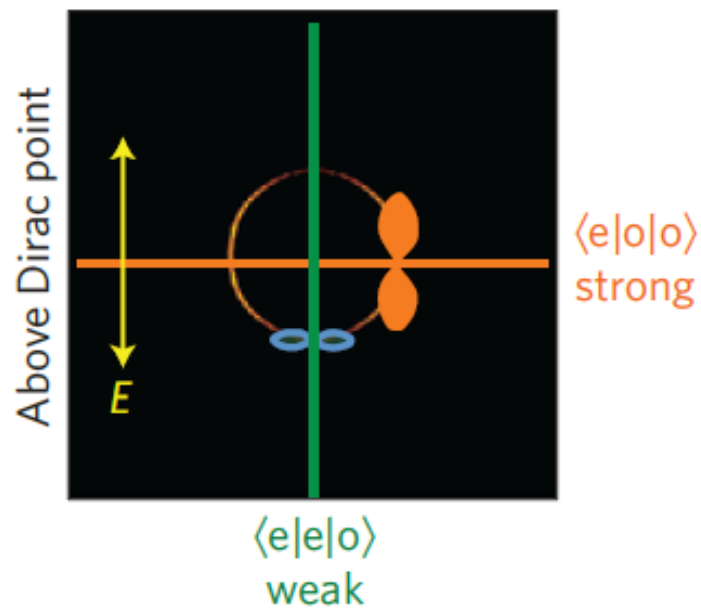


Orbital texture

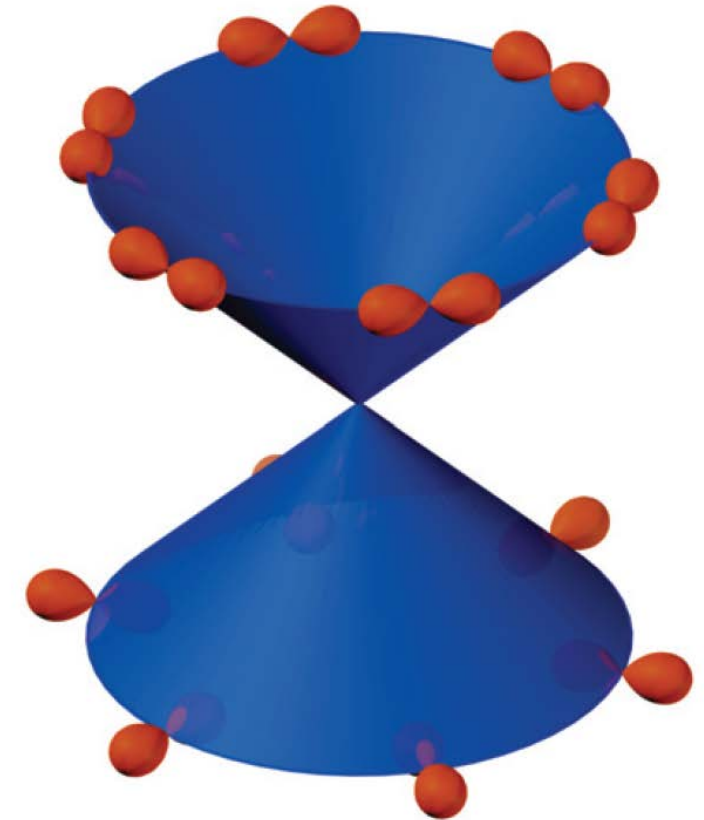
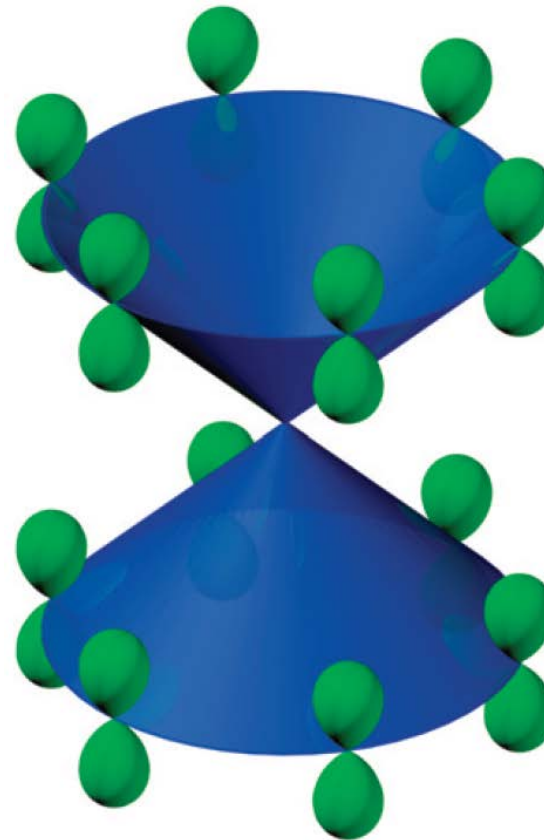
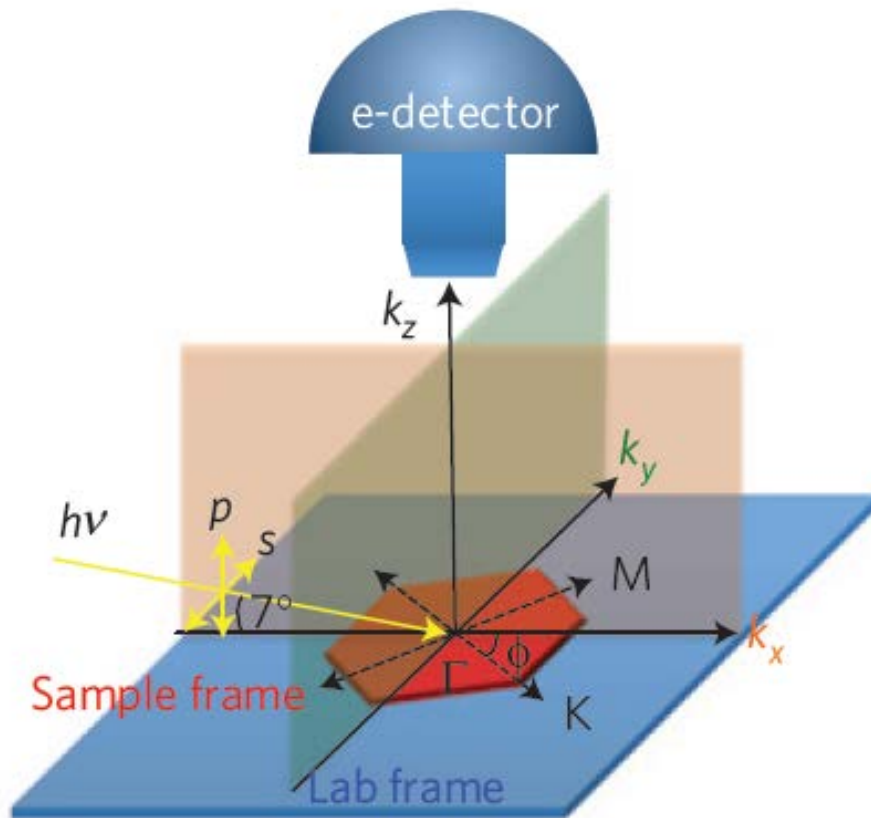


ARPES "matrix element"

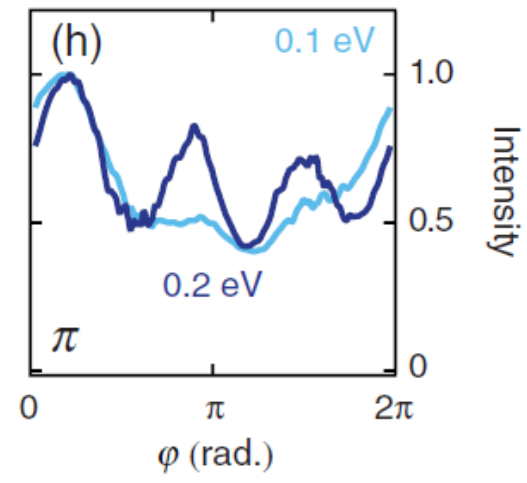
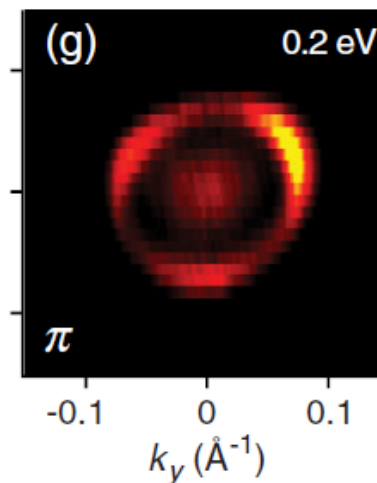
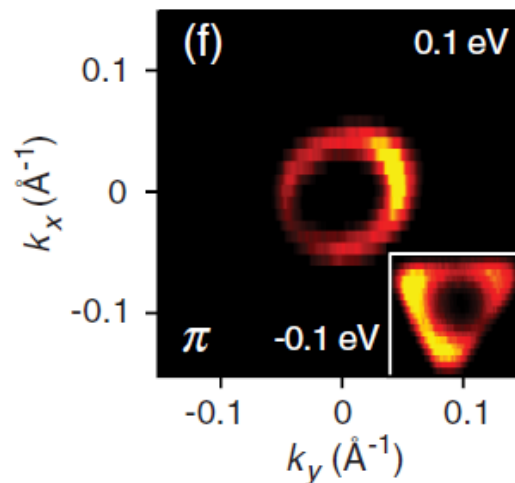
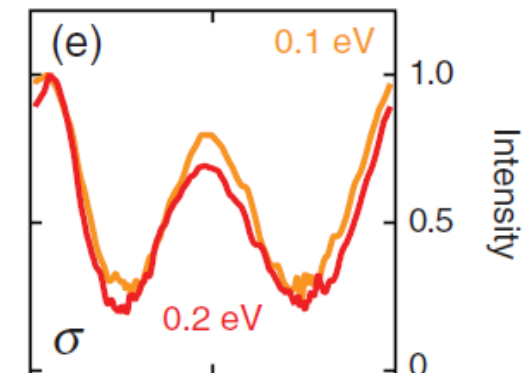
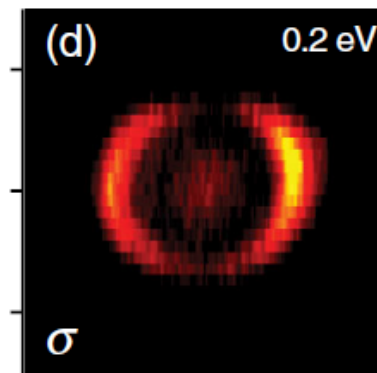
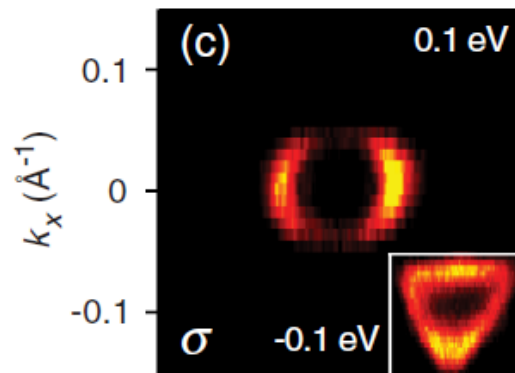
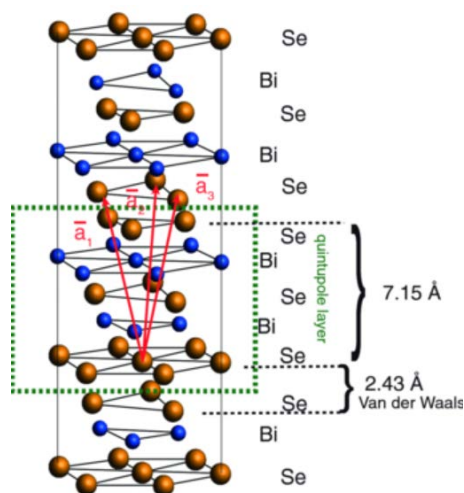
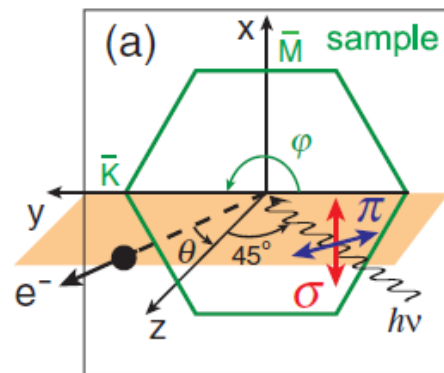
$$\langle \psi_f | A \cdot p | \psi_i \rangle$$



Orbital texture

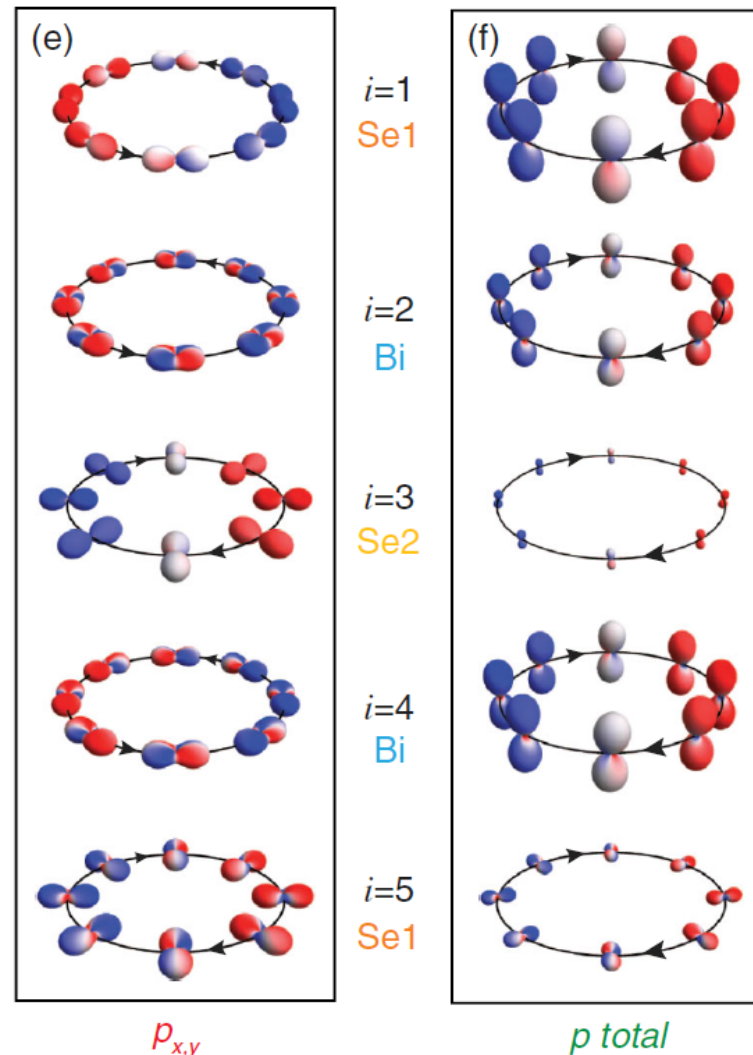
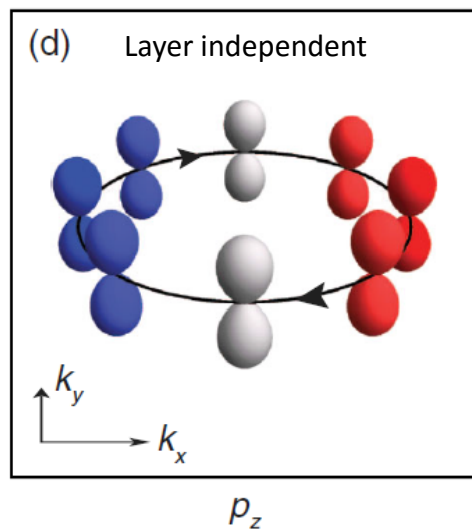
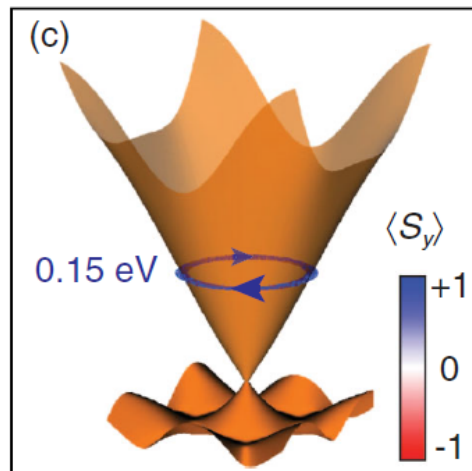
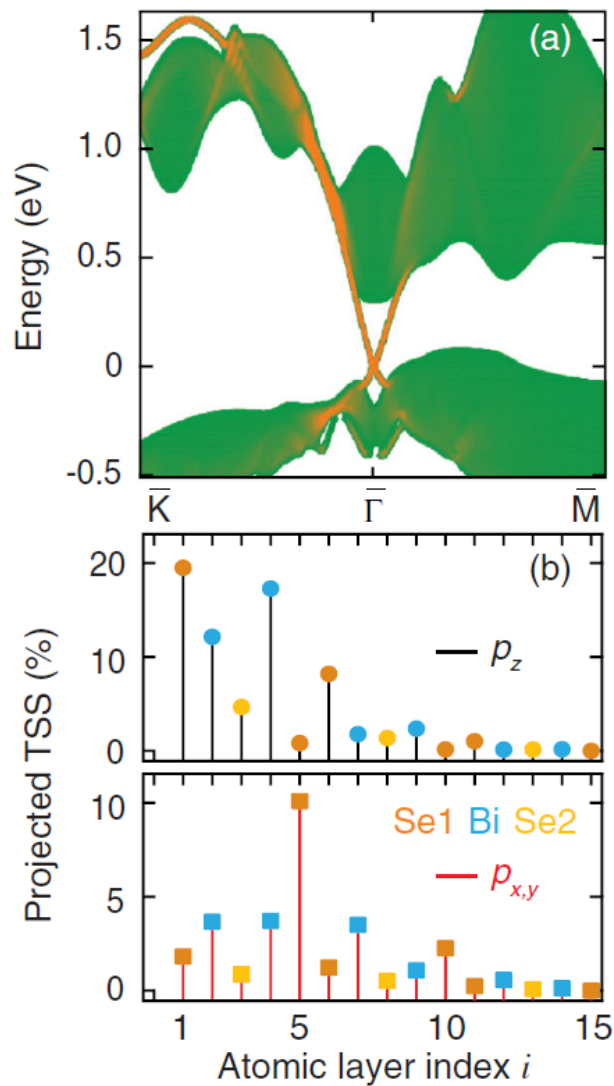


Orbital texture



Layer-dependent spin-orbit texture

DFT 250-layer slab



Layer-dependent orbital texture manifested in ARPES

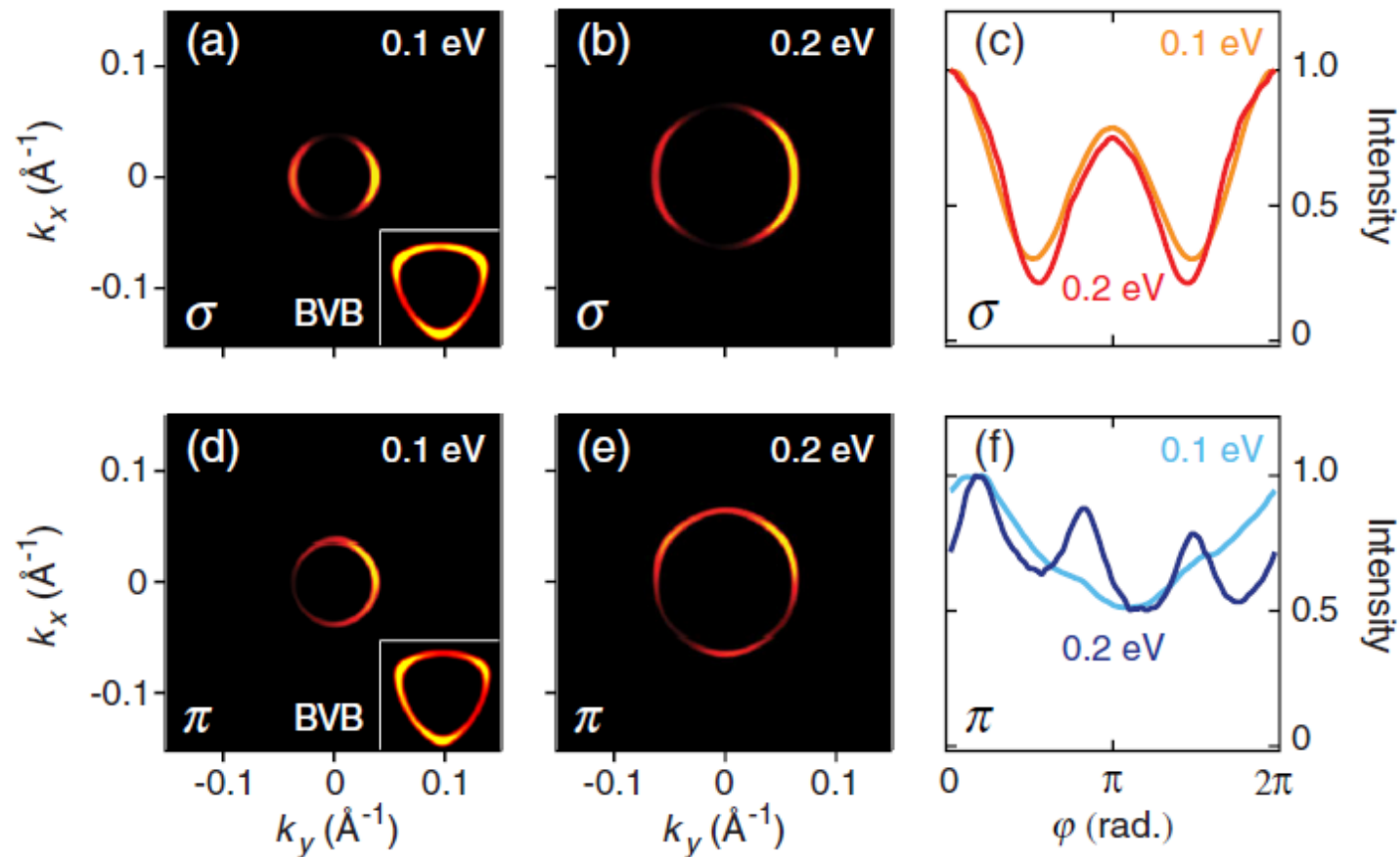
$$I \propto |\langle e^{i\mathbf{k}\cdot\mathbf{r}} | \mathbf{A} \cdot \mathbf{p} | \Psi_{\text{TSS}} \rangle|^2$$

$$\Psi_{\text{TSS}} = \sum_{i,\sigma} \alpha_i \psi_{i,\mathbf{k}_{\parallel}}^{\sigma}$$

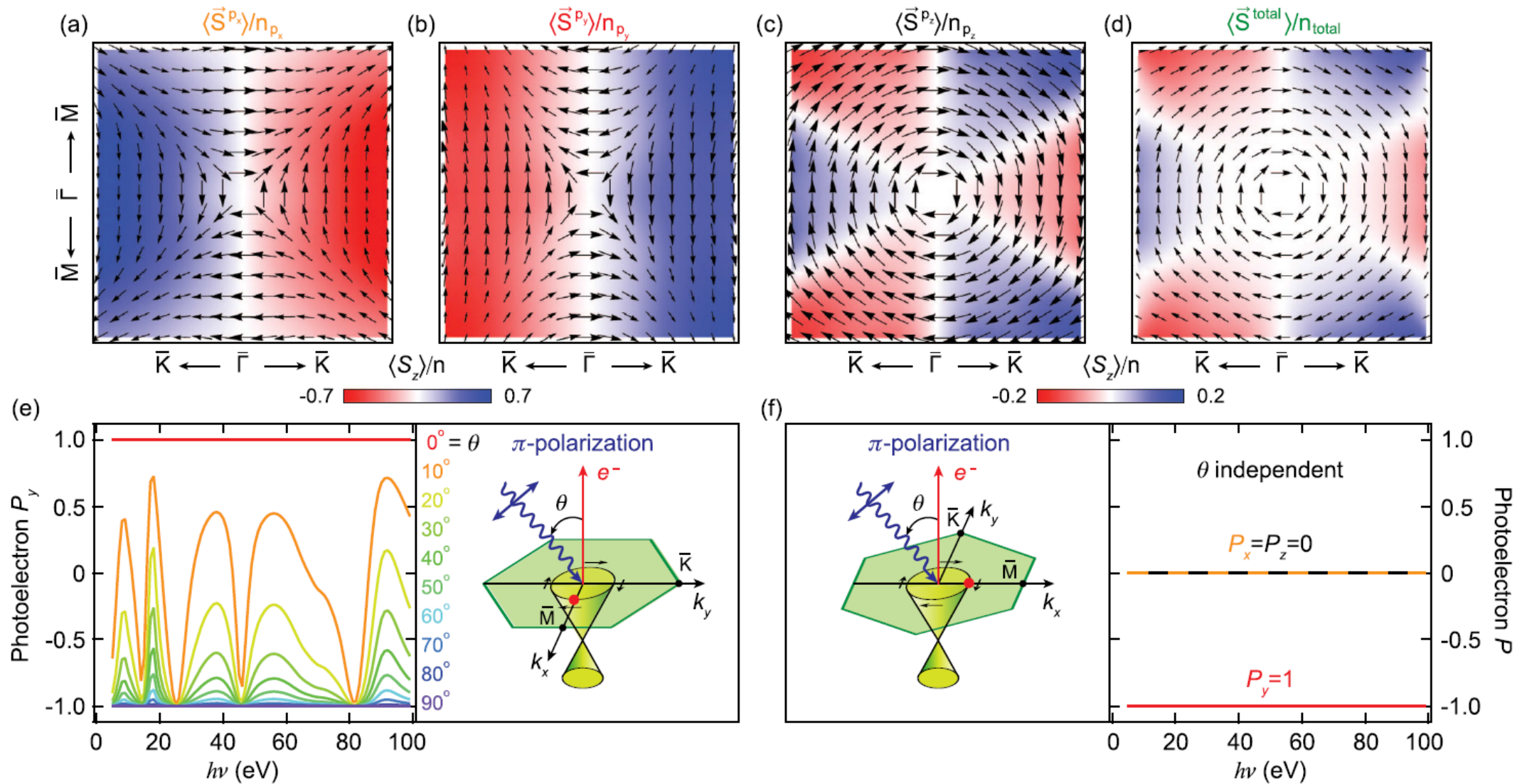
↙
↘
 layer spin

$$I \propto \sum_{\sigma} |\sum_i e^{-ik_z z_i} \langle e^{i\mathbf{k}_{\parallel}\cdot\mathbf{r}_{\parallel}} | \mathbf{A} \cdot \mathbf{p} | \alpha_i \psi_{i,\mathbf{k}_{\parallel}}^{\sigma} \rangle|^2$$

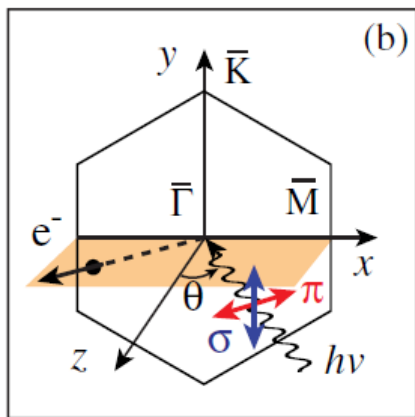
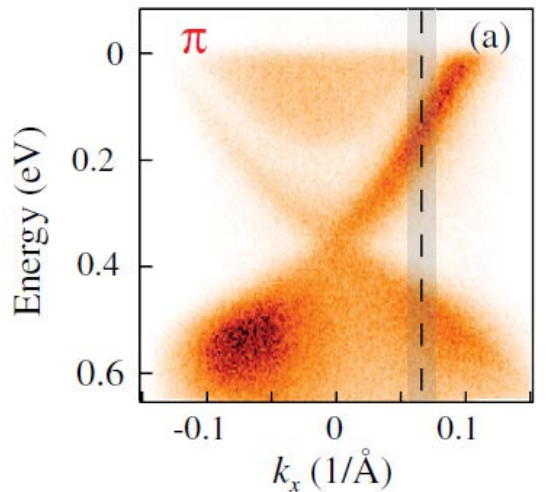
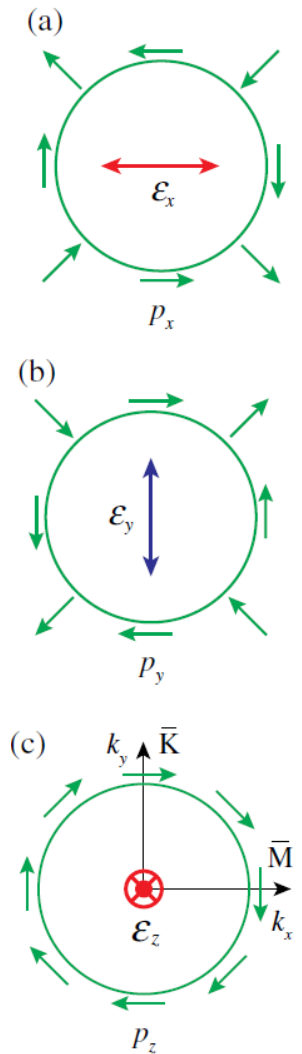
Based on DFT slab calculations



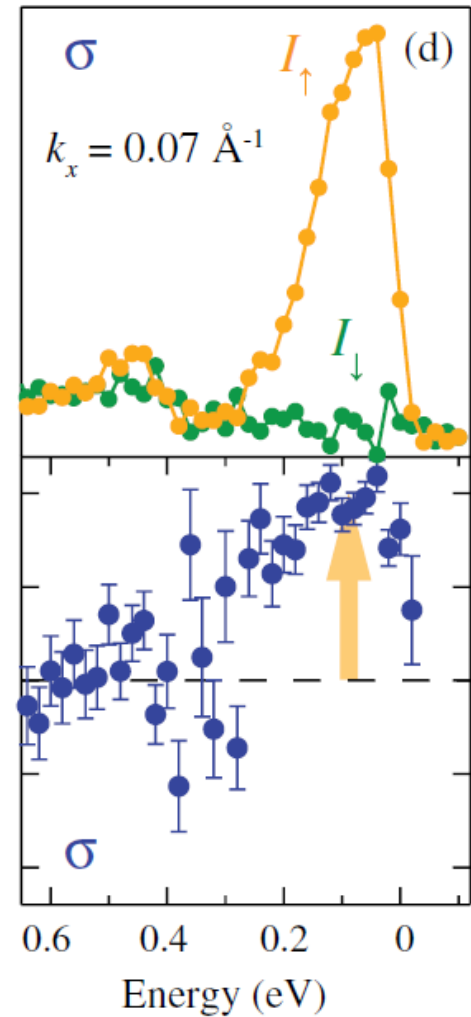
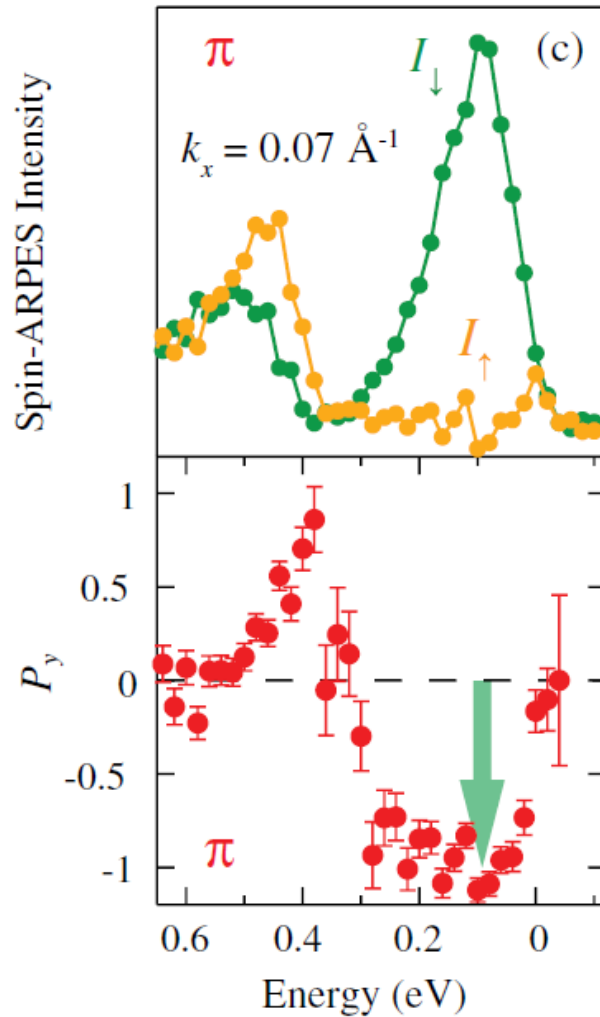
Spin-orbital texture



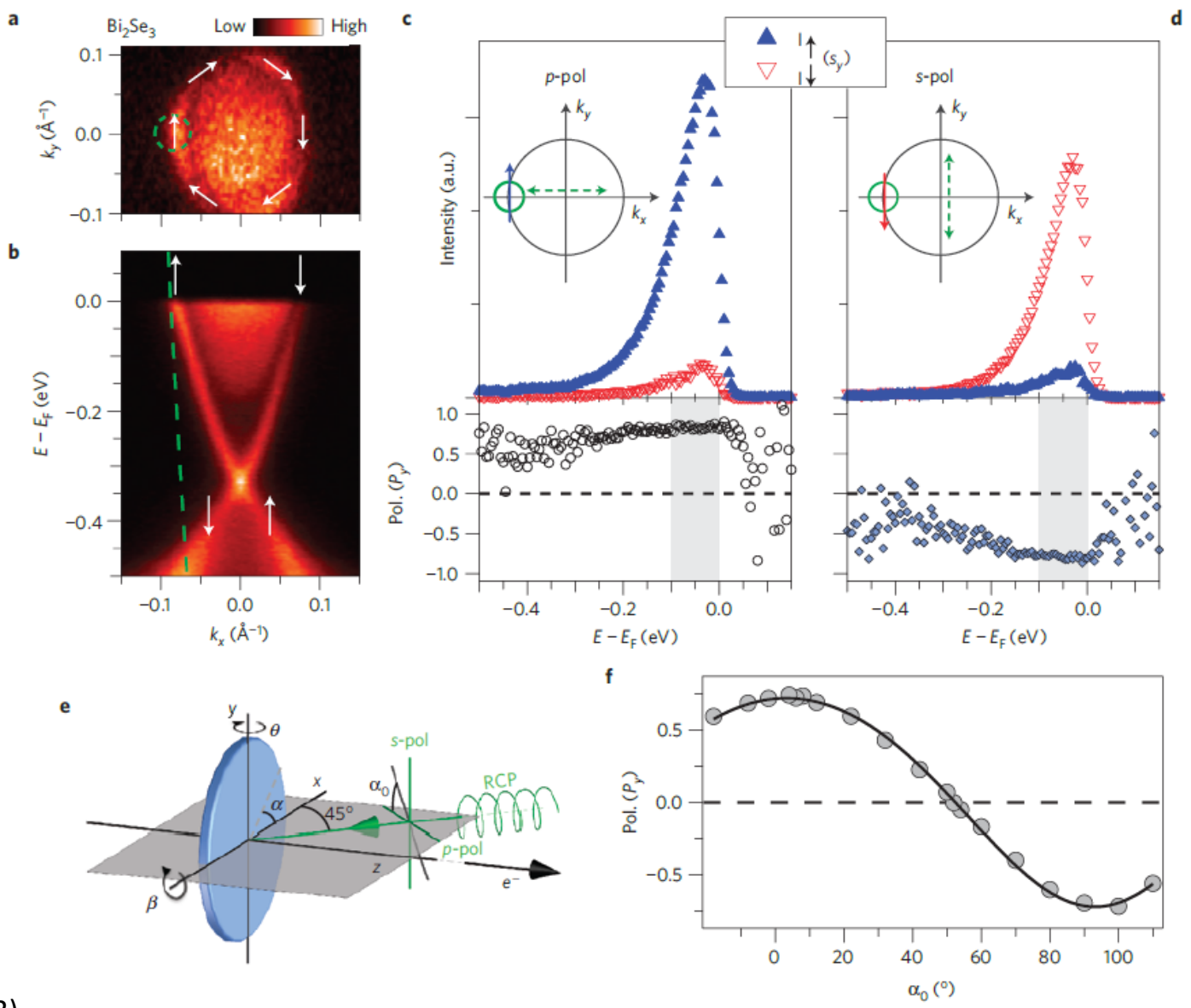
Polarization control of photoelectron spin



y-component of spin




Polarization control of photoelectron spin



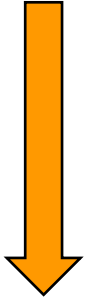
Correlated topological insulators – 5d transition metal oxides

U



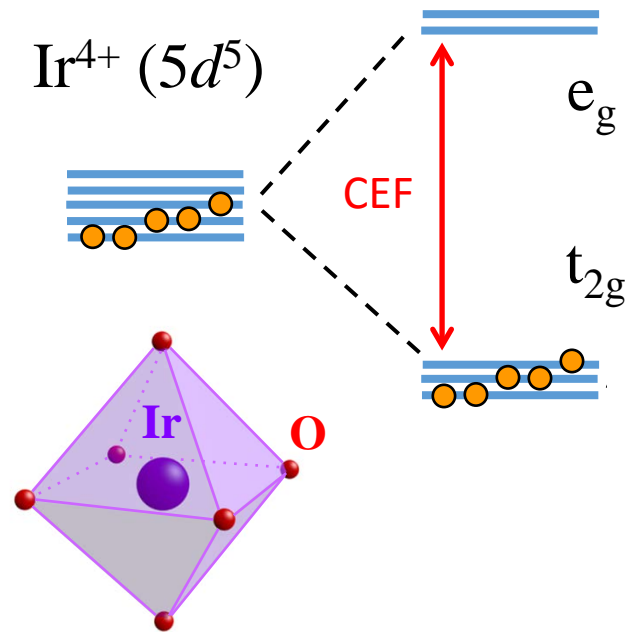
1 H	2 He																
3 Li	4 Be	5 B	6 C	7 N	8 O	9 F	10 Ne										
11 Na	12 Mg	13 Al	14 Si	15 P	16 S	17 Cl	18 Ar										
19 K	20 Ca	21 Sc	22 Ti	23 V	24 Cr	25 Mn	26 Fe	27 Co	28 Ni	29 Cu	30 Zn	31 Ga	32 Ge	33 As	34 Se	35 Br	36 Kr
37 Rb	38 Sr	39 Y	40 Zr	41 Nb	42 Mo	43 Tc	44 Ru	45 Rh	46 Pd	47 Ag	48 Cd	49 In	50 Sn	51 Sb	52 Te	53 I	54 Xe
55 Cs	56 Ba	57 La	72 Hf	73 Ta	74 W	75 Re	76 Os	77 Ir	78 Pt	79 Au	80 Hg	81 Tl	82 Pb	83 Bi	84 Po	85 At	86 Rn
87 Fr	88 Ra	89 Ac	104 Rf	105 Db	106 Sg	107 Bh	108 Hs	109 Mt	110 Ds	111 Rg	112 Uub	113 Uut	114 Uuq	115 Uup			

SOC,
CEF



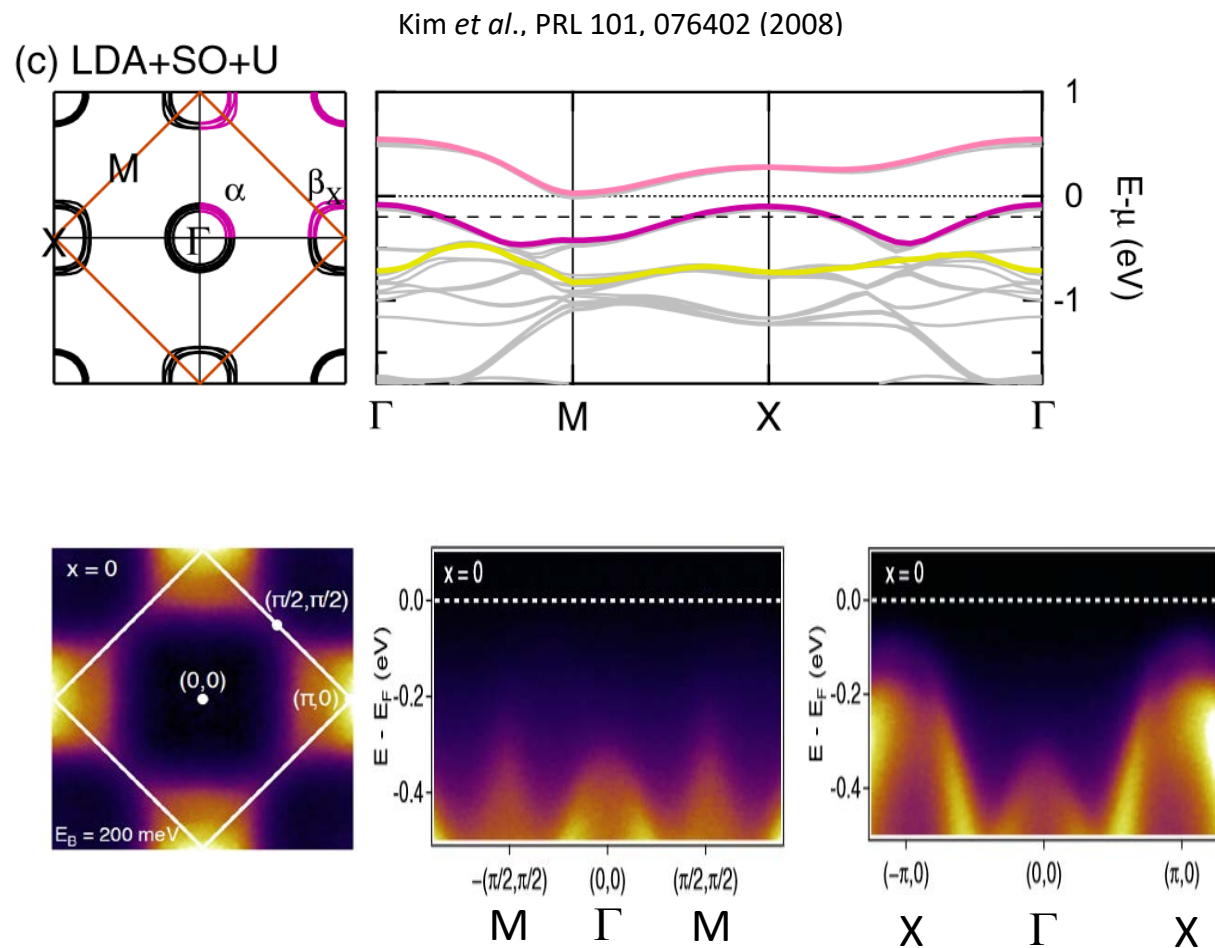
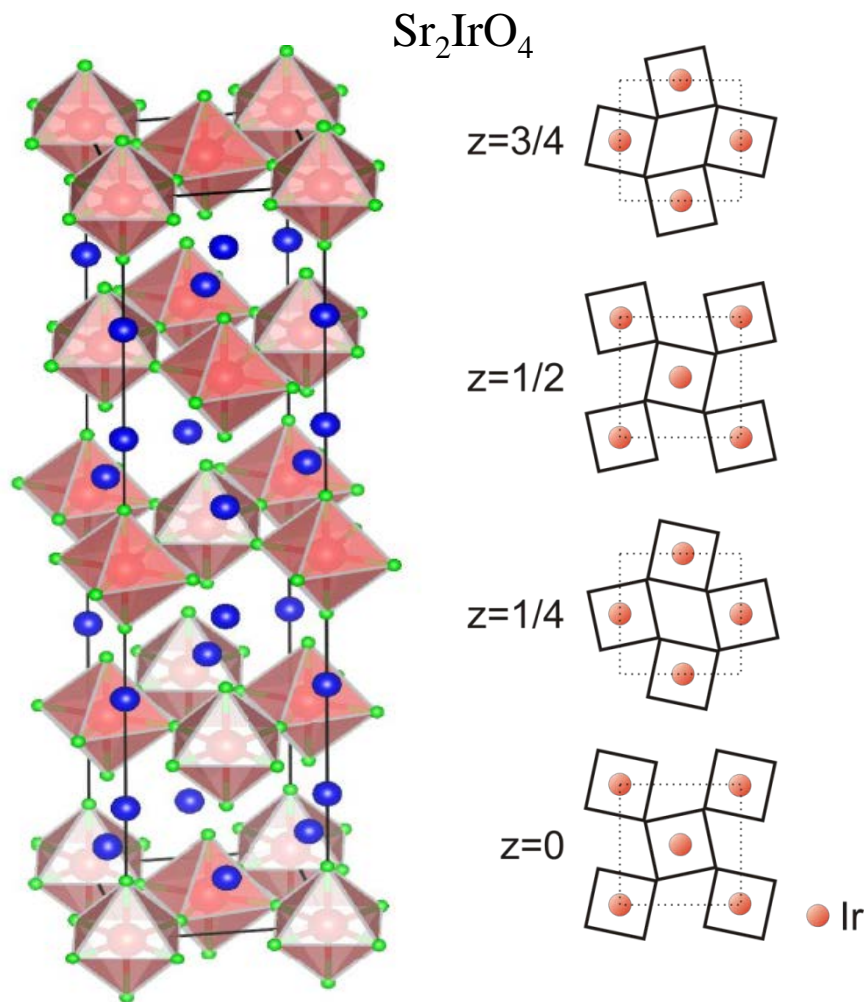
- Interplay between electron correlations, crystal electric field and spin-orbit coupling and ($U \sim \text{SOC} \sim \text{CEF}$)
- Potential for exotic physics driven by strong SOC ($\sim 0.5\text{eV}$)

$J_{\text{eff}} = 1/2$ Mott insulators in $5d$ systems



The Ruddlesden-Popper series ($\text{Sr}_{n+1}\text{Ir}_n\text{O}_{3n+1}$)

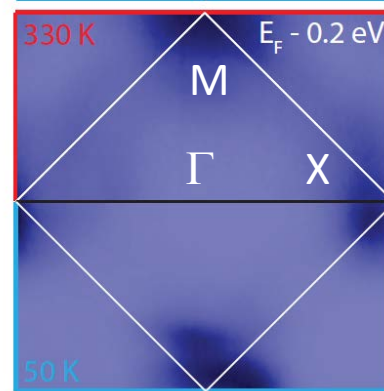
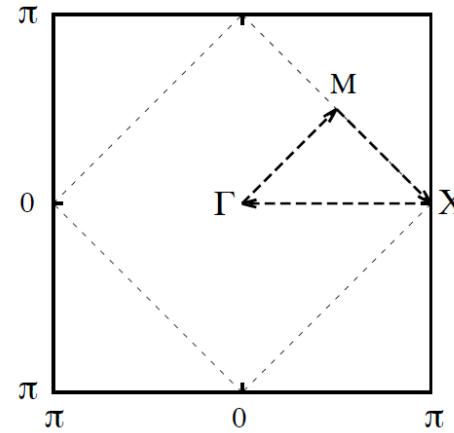
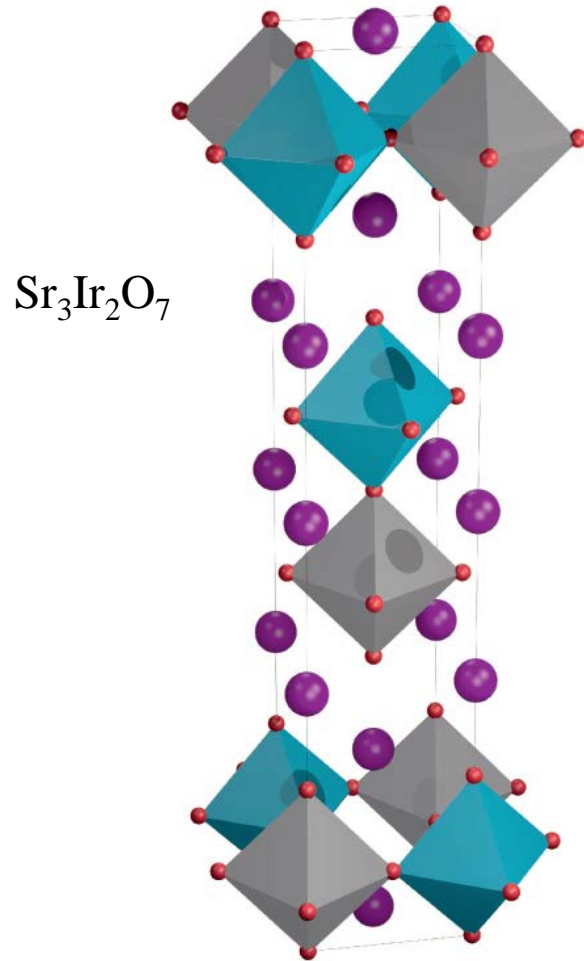
$n = 1$ single layer (insulator)



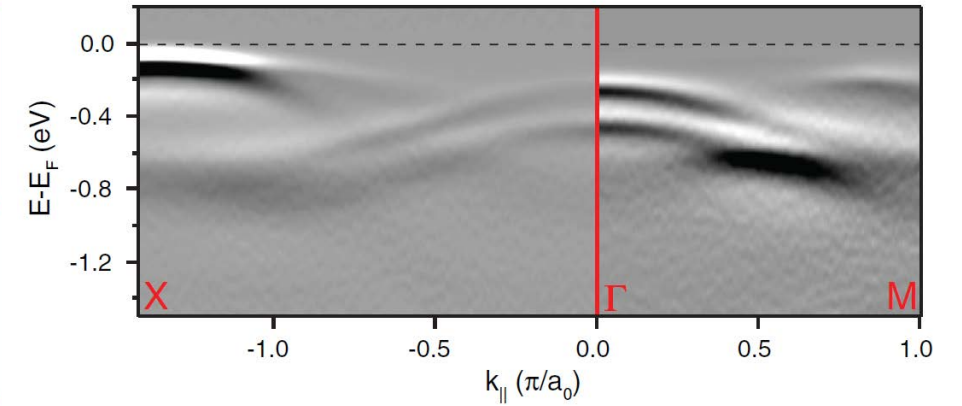
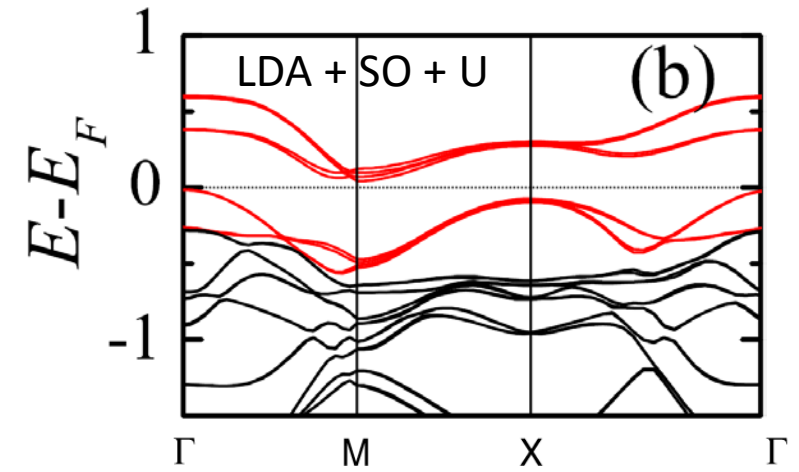
de la Torre *et al.*, PRL 115, 176402 (2015)

The Ruddlesden-Popper series ($\text{Sr}_{n+1}\text{Ir}_n\text{O}_{3n+1}$)

$n = 2$ bilayer (insulator)



Moon *et al.*, PRL 101, 226402 (2008)



King *et al.*, PRB 87, 241106(R) (2013)

The Ruddlesden-Popper series ($\text{Sr}_{n+1}\text{Ir}_n\text{O}_{3n+1}$)

$n = \infty$ infinite layer

SrIrO_3 : orthorhombic Pbnm

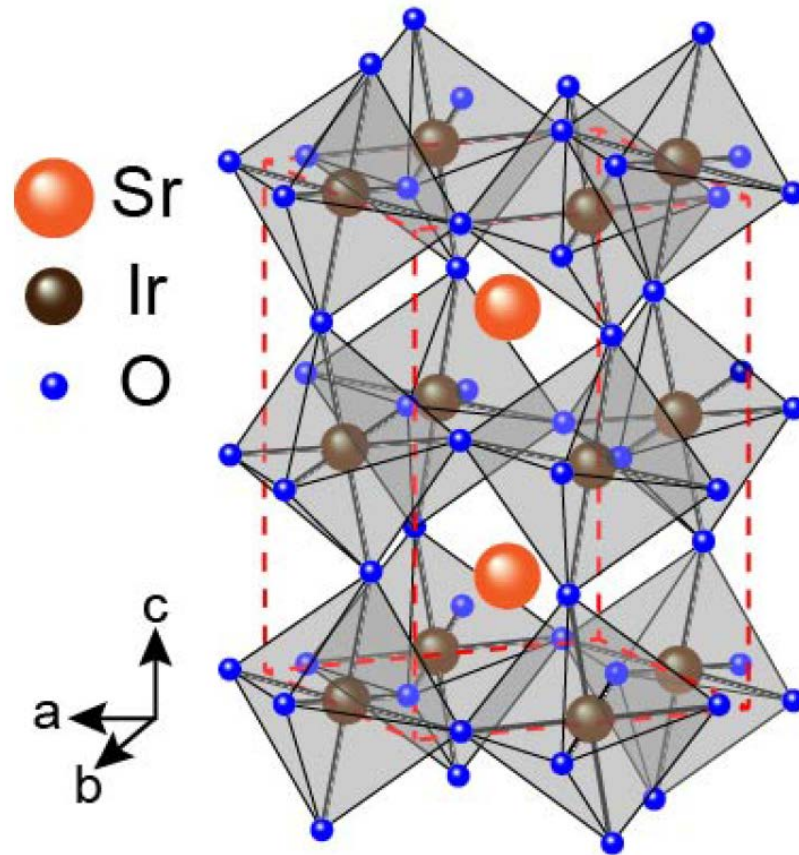
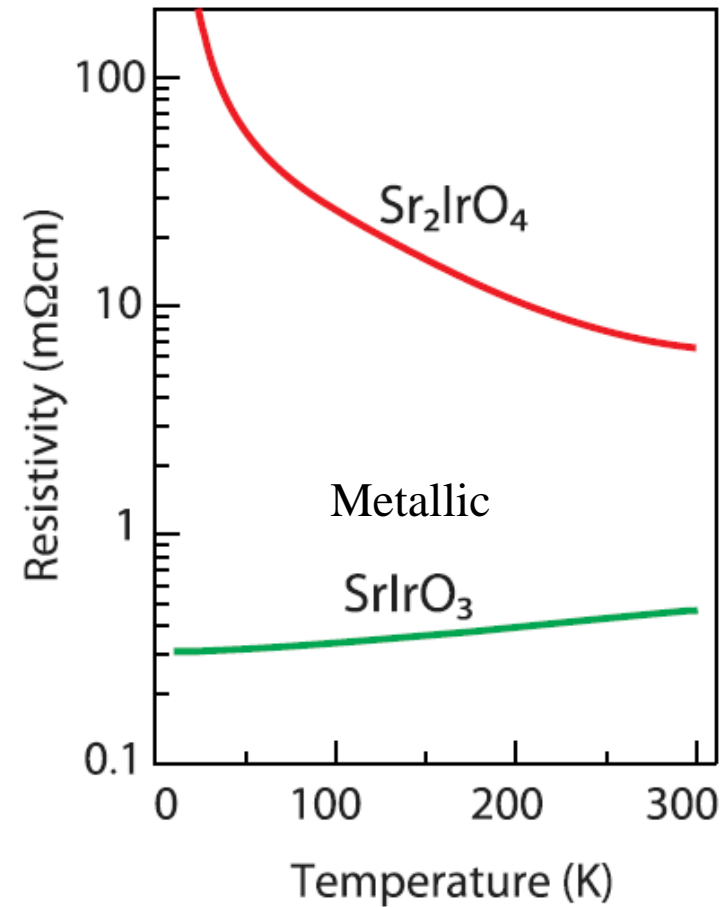
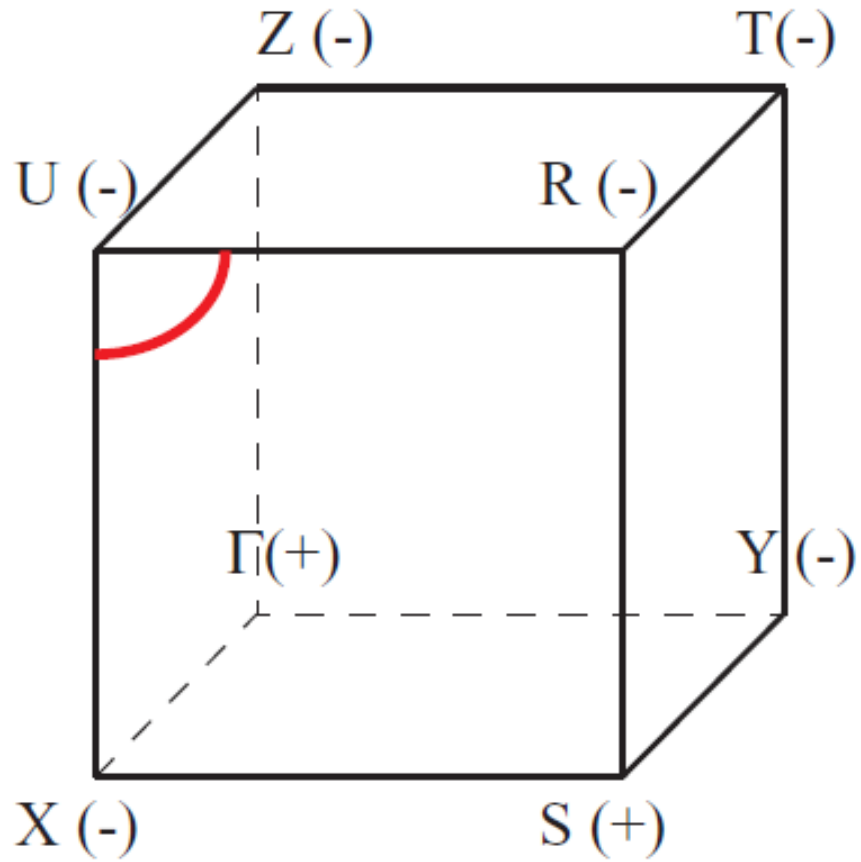


Image: Liu *et al.*, ArXiv:1501:00654 (2015)

Nie *et al.*, PRL 114, 016401 (2015)

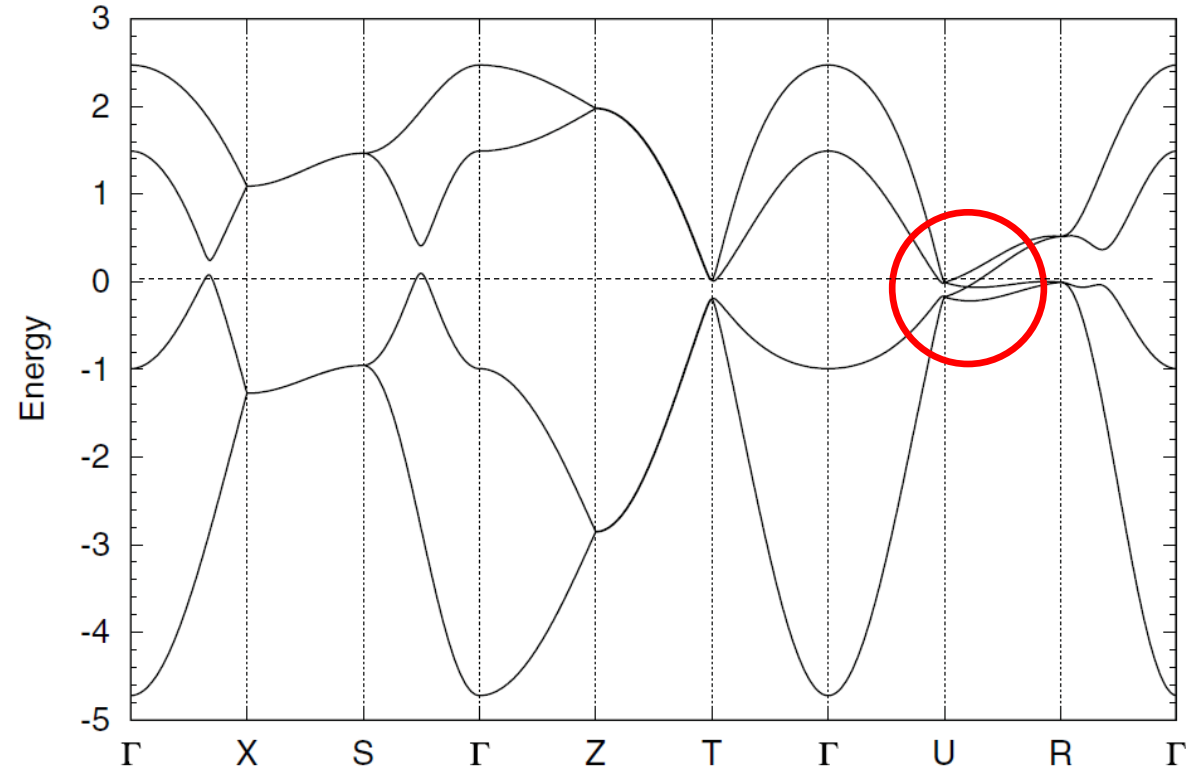


Semi-metallic SrIrO₃ – band structure



Tight-binding model with only $J_{\text{eff}} = \frac{1}{2}$ states

Carter *et al.*, PRB 85, 115105 (2012)

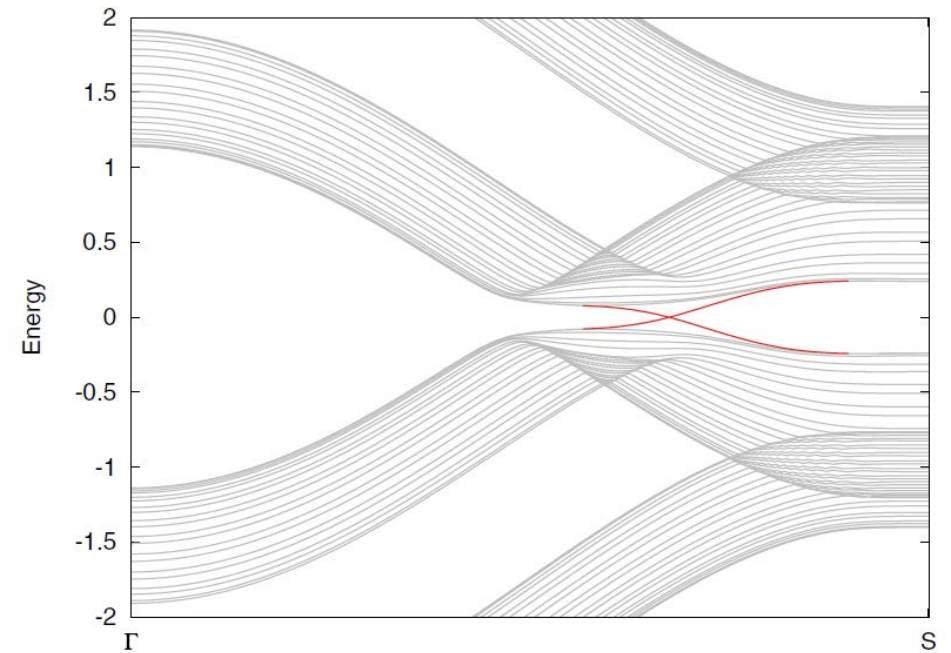
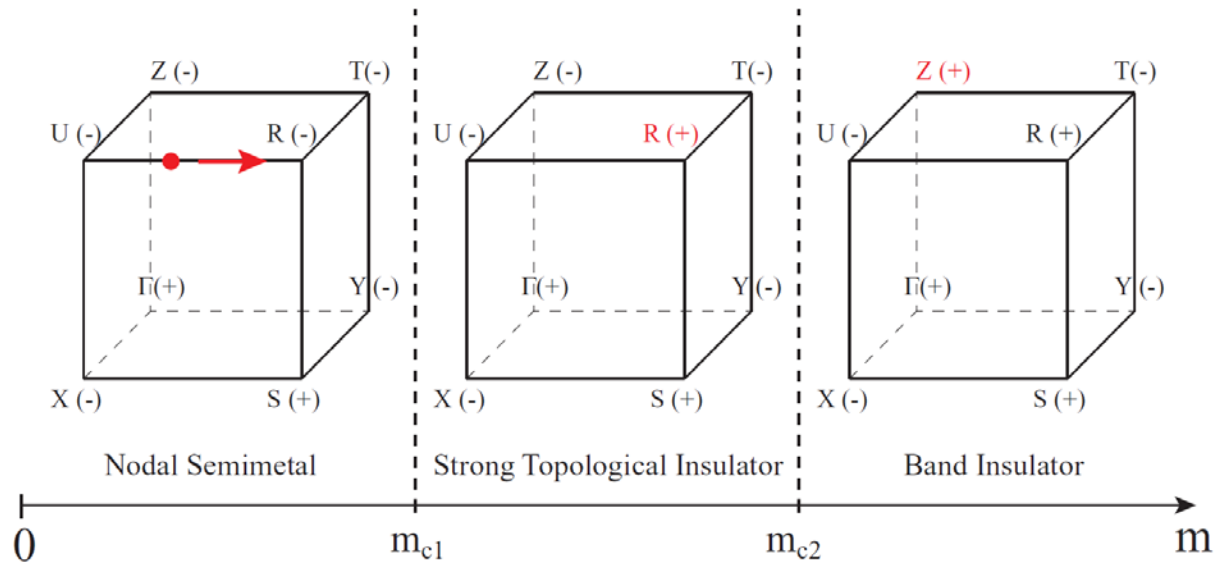


Node near U protected by n -glide symmetry

Liu *et al.*, ArXiv:1506:03559 (2015)

Semi-metallic \rightarrow semi-conducting transition in SrIrO_3

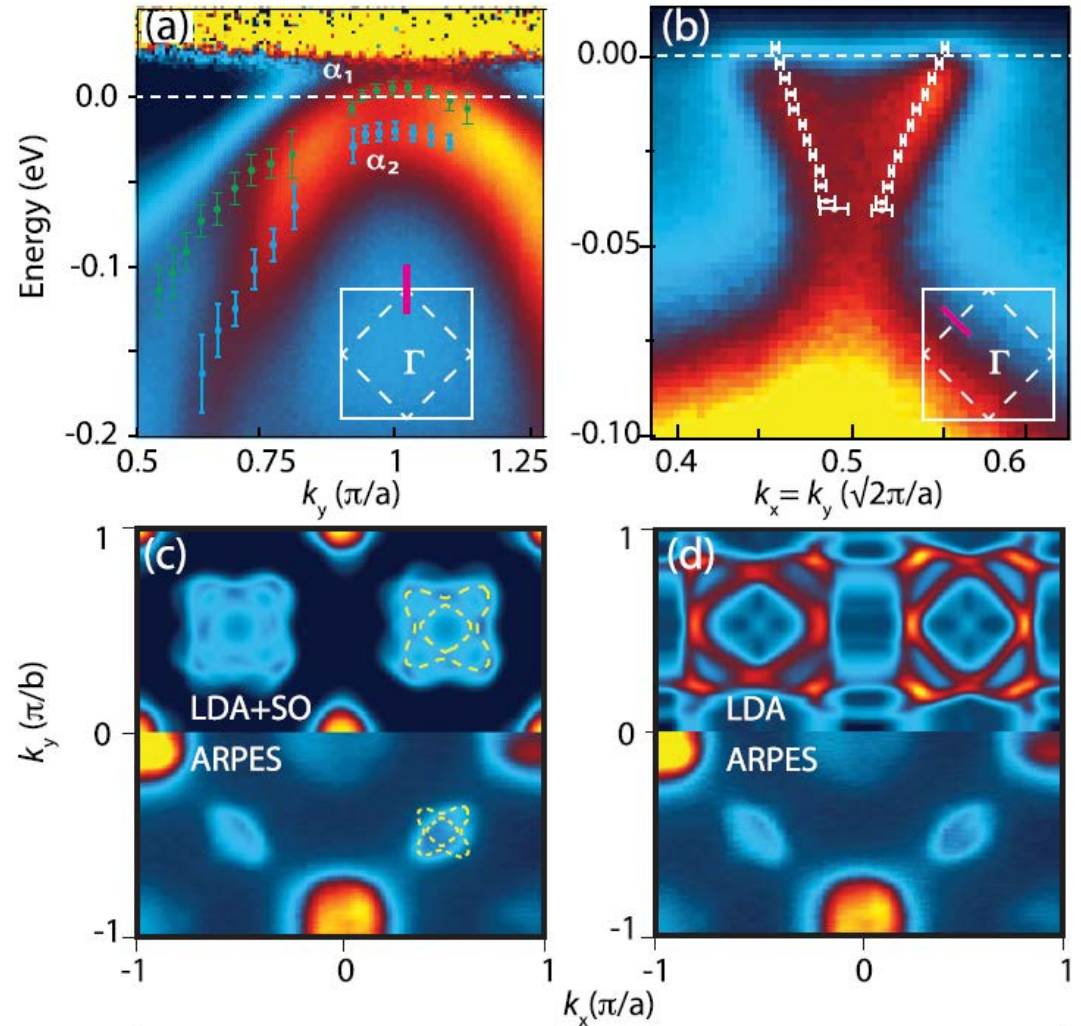
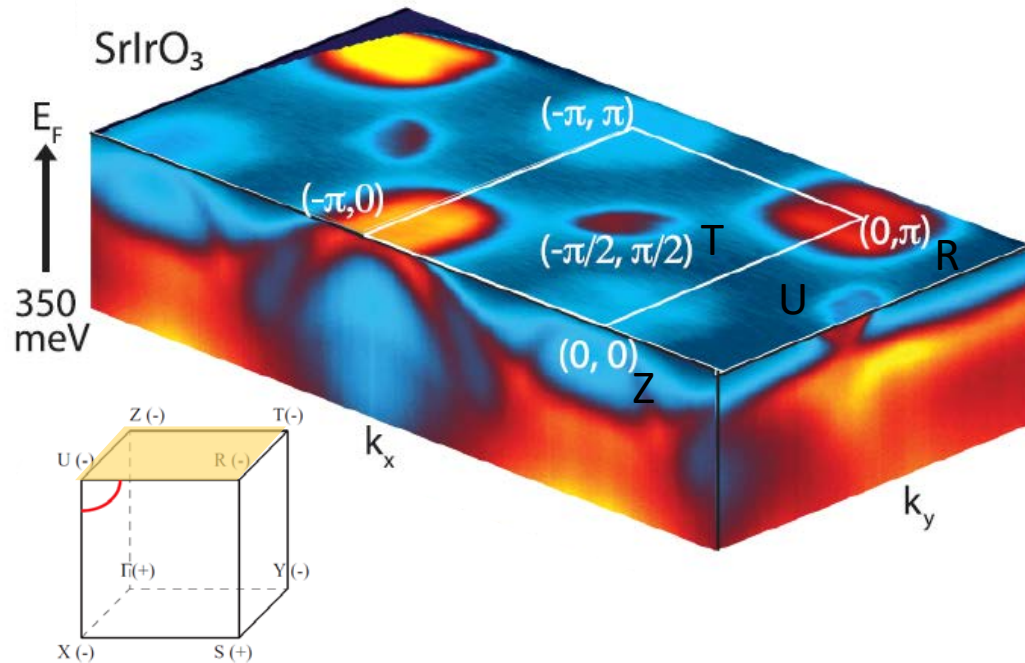
Add staggered sublayer potential or SOC term: $m\sigma_x$
 ($\sigma_x = \text{layer index}$)



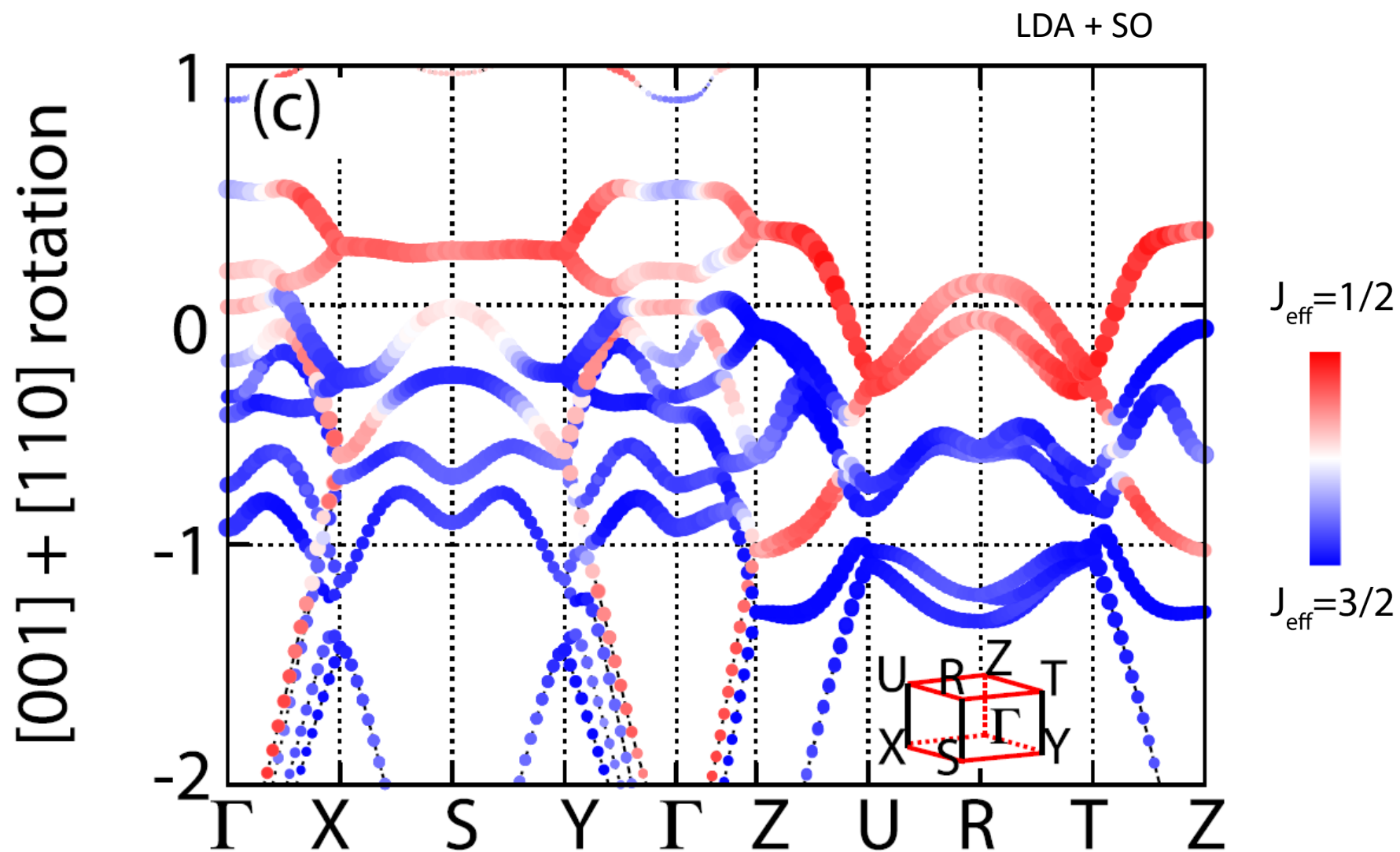
SrIrO₃ thin film - ARPES

No bulk single crystals available yet
Pseudo-cubic structure difficult to cleave

MBE grown SrIrO₃(001) on LSAT

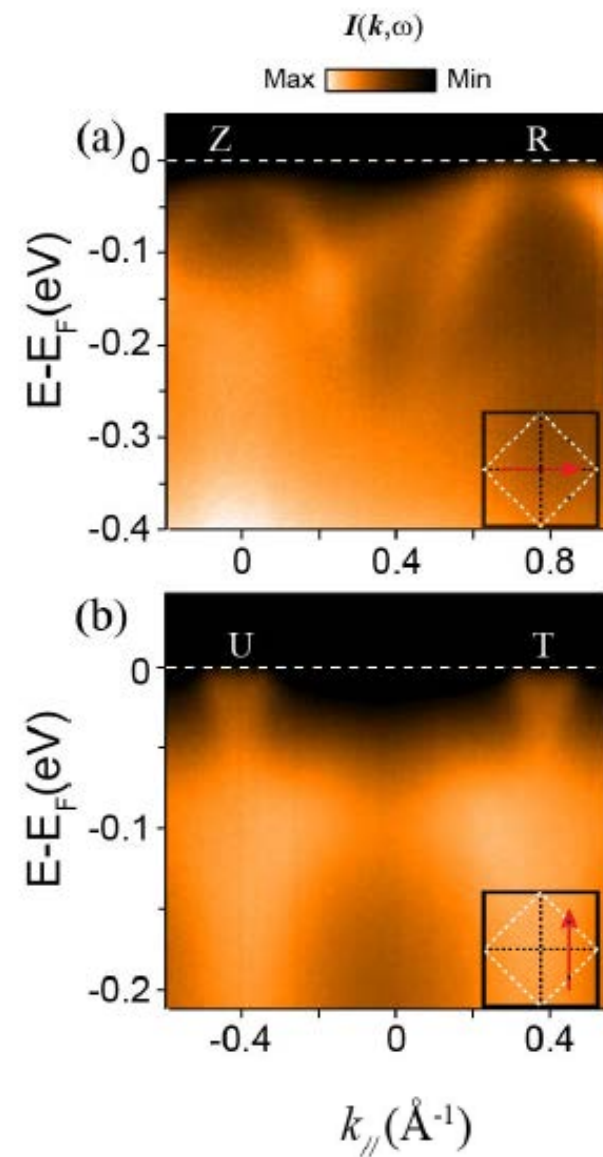
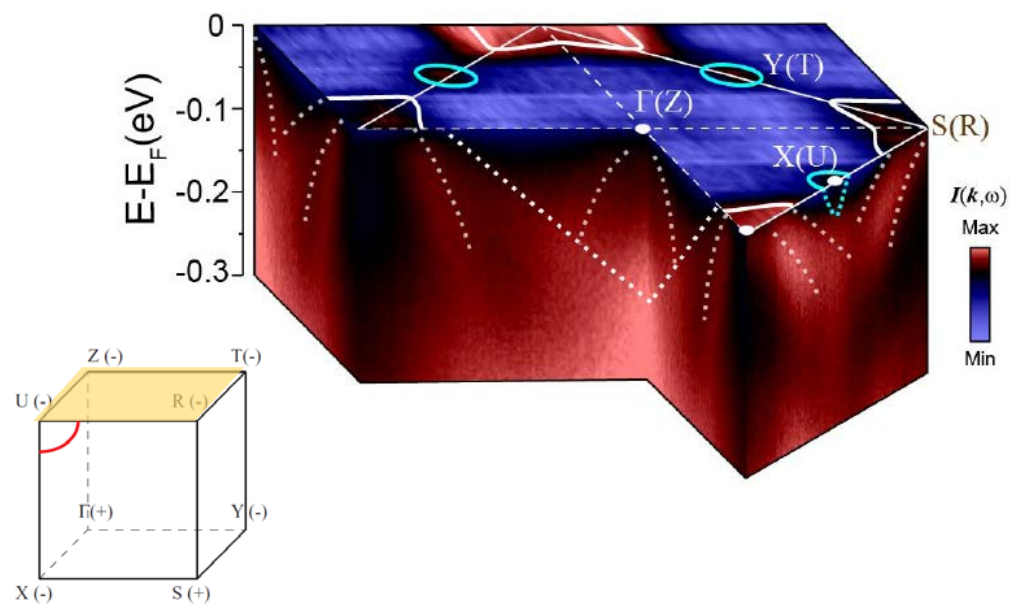


LDA band structure of SrIrO₃

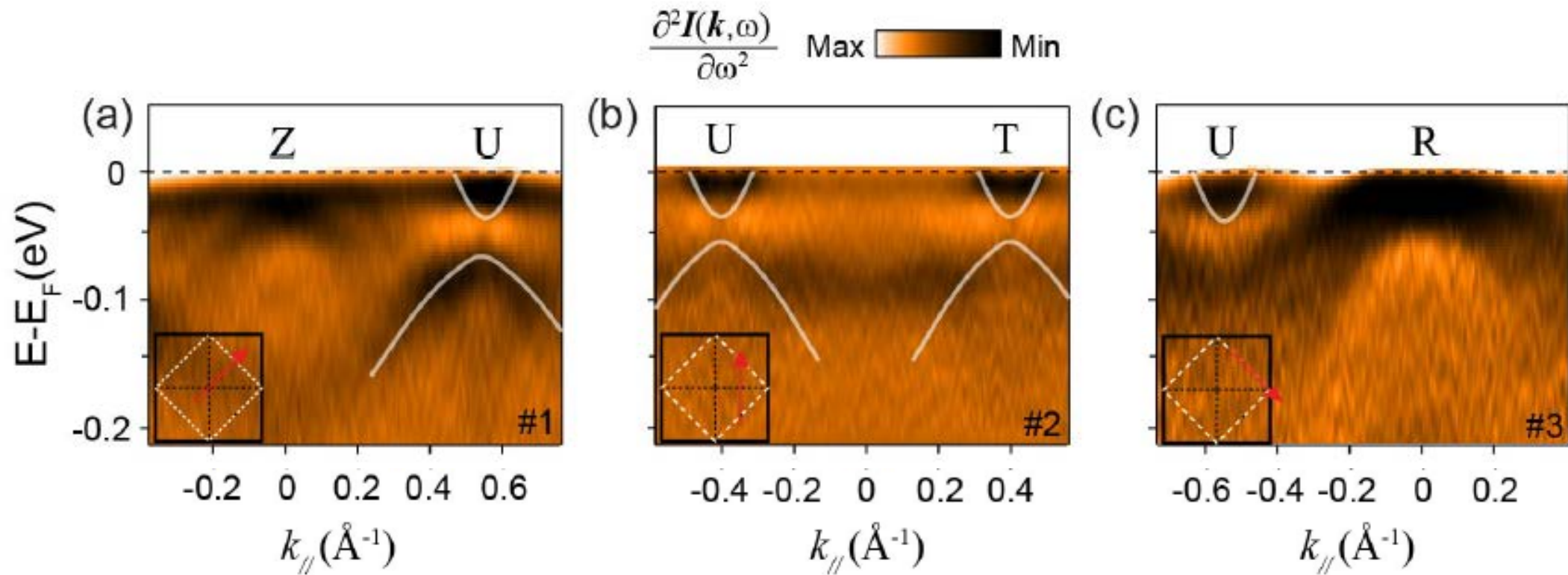


SrIrO₃ thin film - ARPES

MBE grown SrIrO₃(001) on SrTiO₃(001)



SrIrO₃ thin film - ARPES

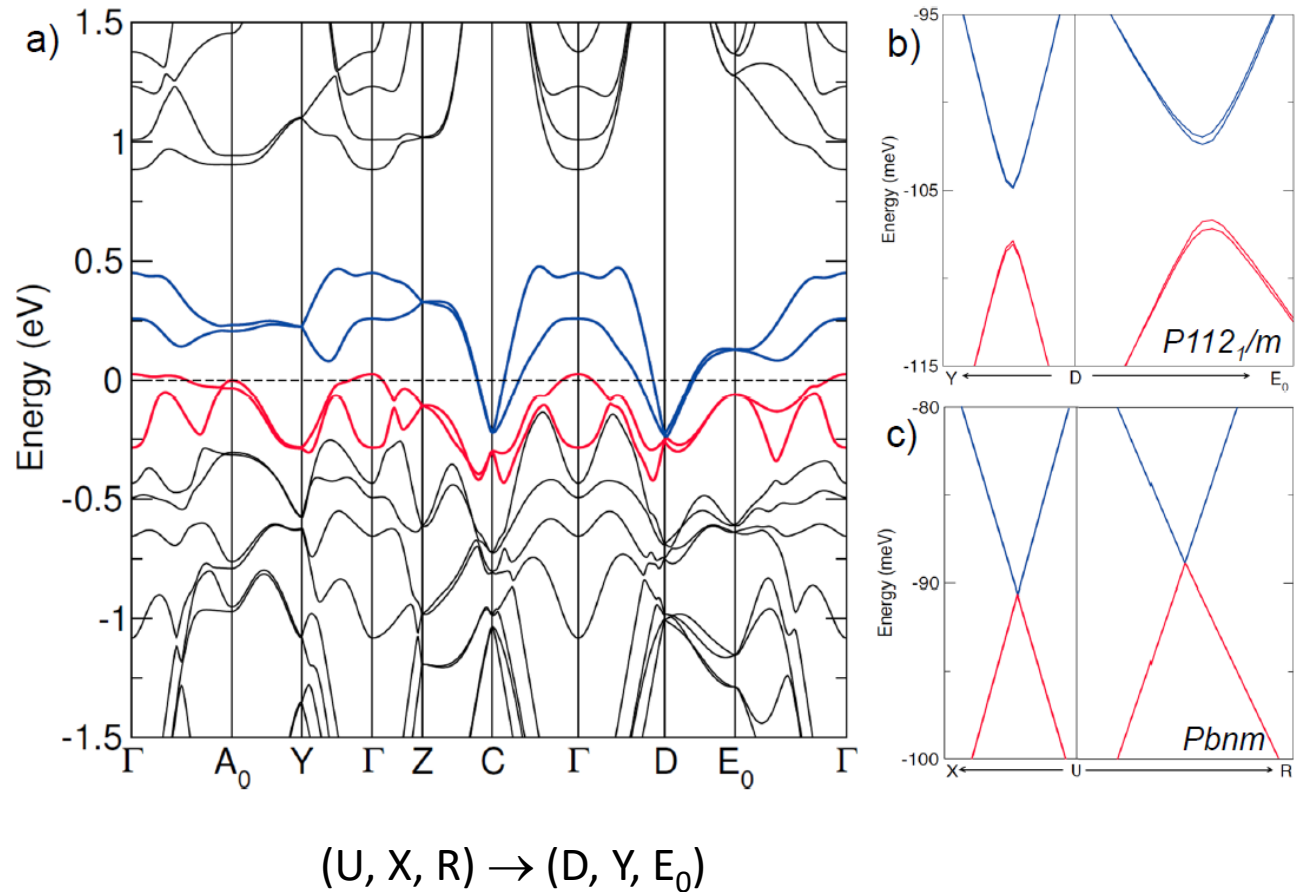
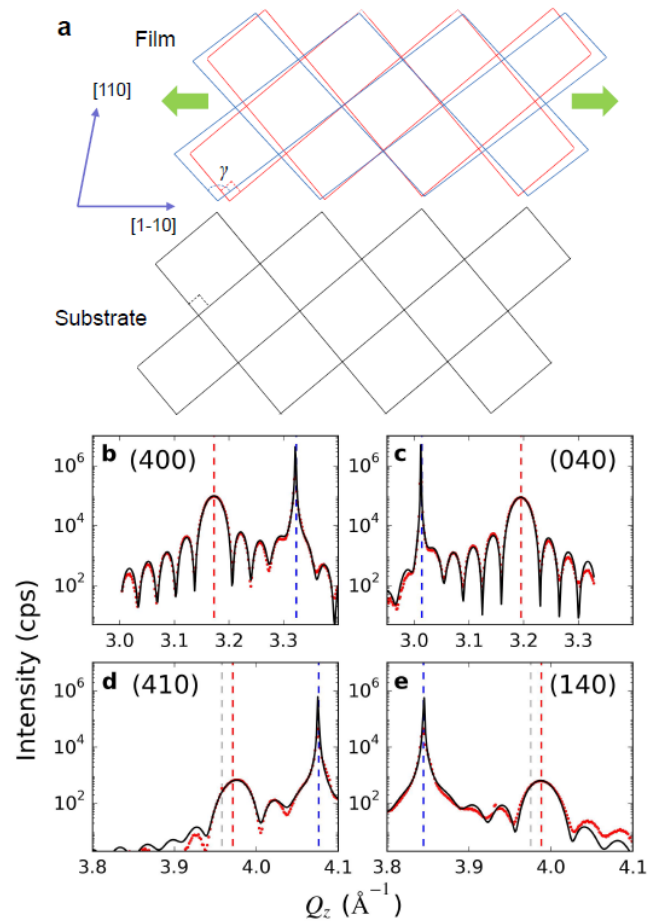


SrIrO₃ thin film - ARPES

PLD grown SrIrO₃(001) on GdScO₃(110)

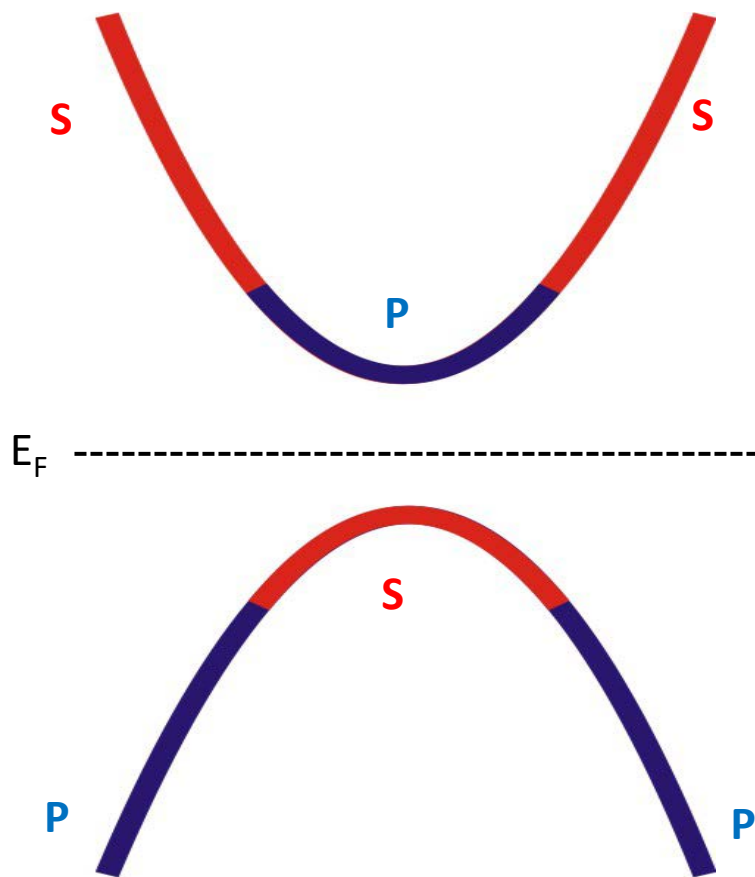
X-ray diffraction shows strain induced monoclinicity

Pbnm → P112₁/m breaks *n*-glide symmetry

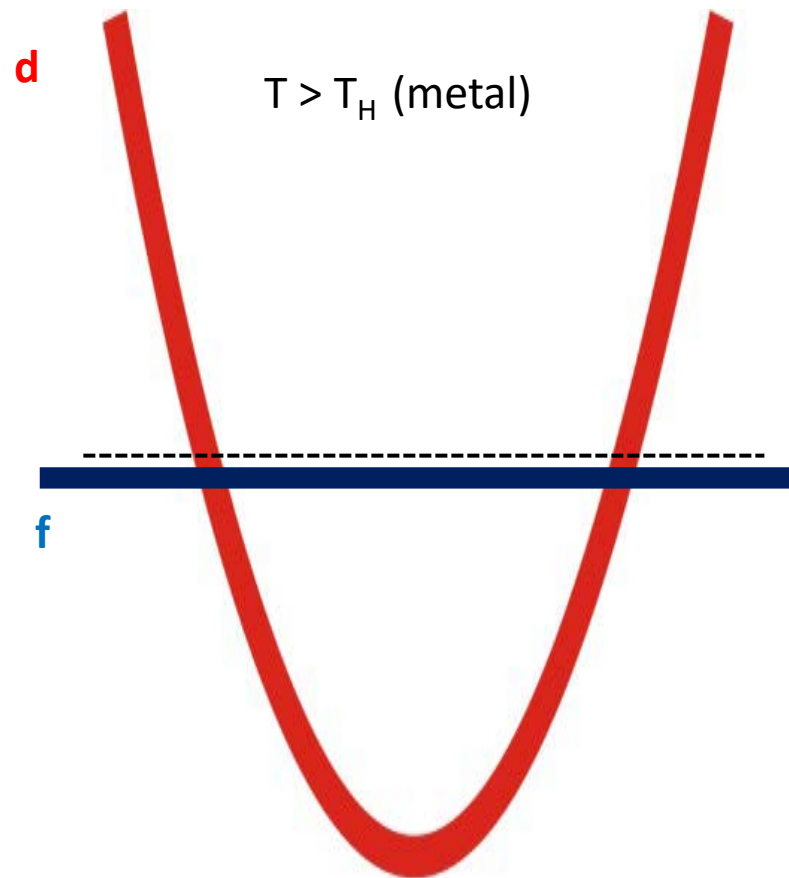


Correlated topological insulators – heavy f -electron materials

SOC Band Insulator

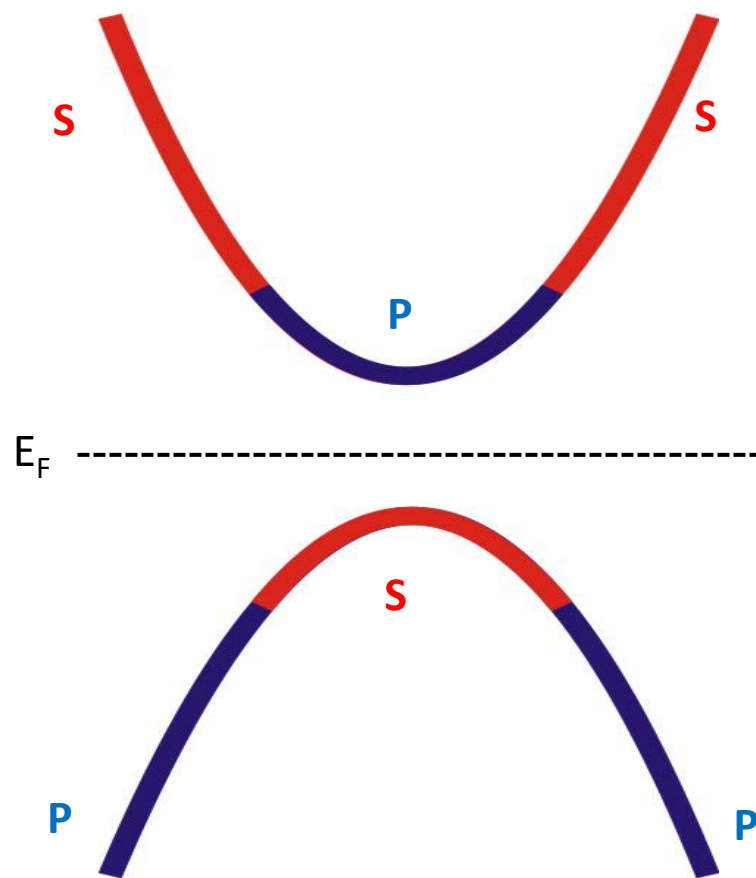


Correlated Kondo Insulator



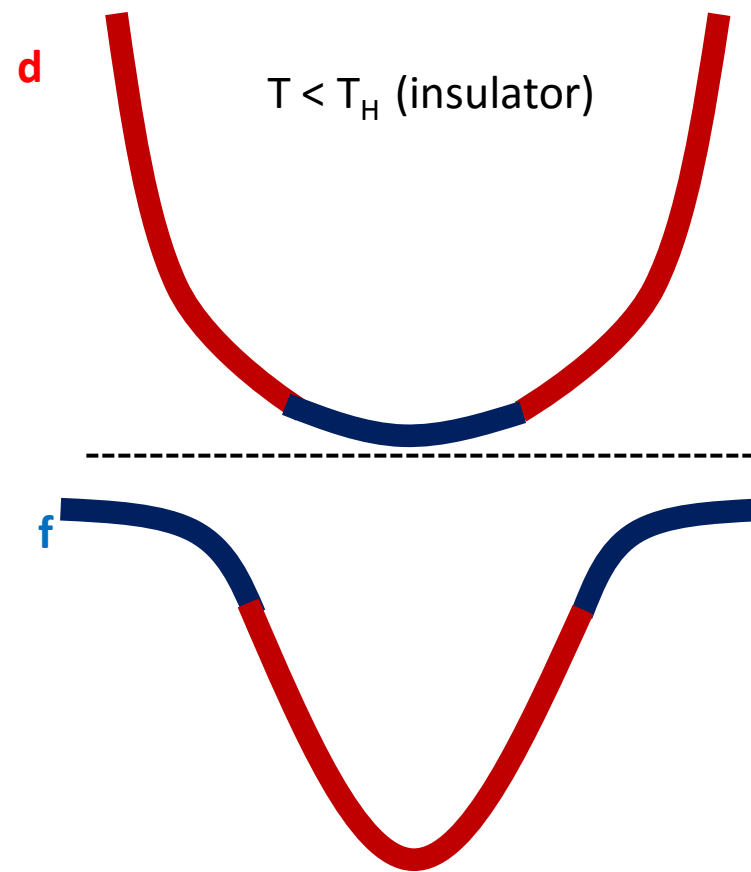
Correlated topological insulators – heavy f -electron materials

SOC Band Insulator



$$\Delta \sim 0.5 \text{ eV} , T = \Delta/k_B \sim 5000 \text{ K}$$

Correlated Kondo Insulator



$$\Delta \sim 10 \text{ meV} , T \sim 100 \text{ K}$$

SmB₆

Lu et al., PRL **110**, 096401 (2013)

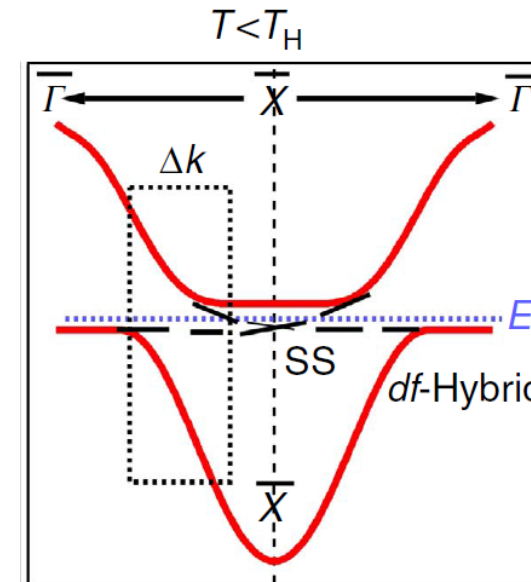
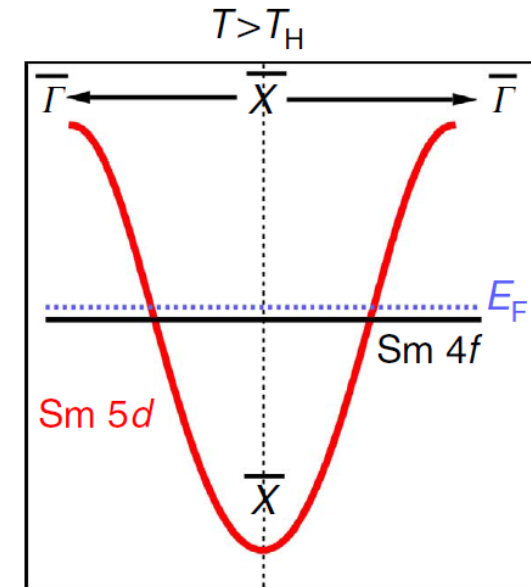
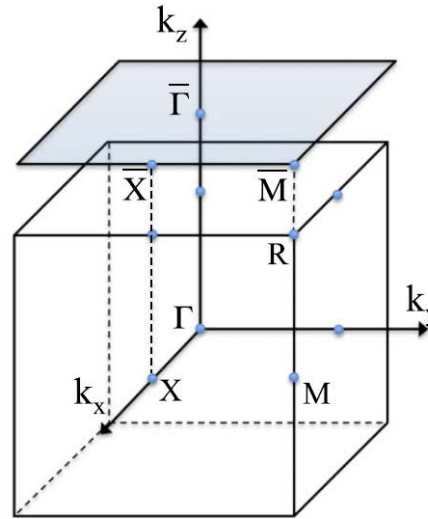
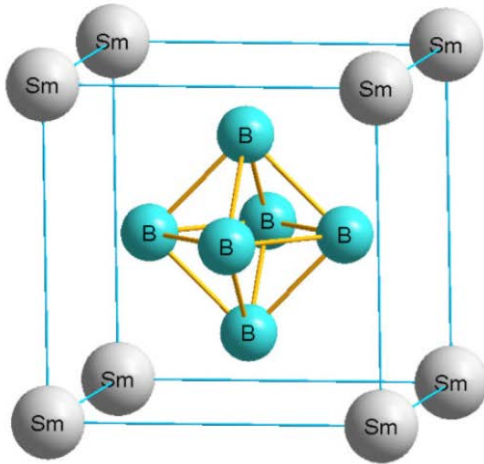


TABLE I. The products of parity eigenvalues of the occupied states for TRIM points, Γ , X , R , and M in the BZ.

Γ	$3X$	R	$3M$
+	-	+	+

M. Dzero *et al.*, PRL **104**, 106408 (2010).

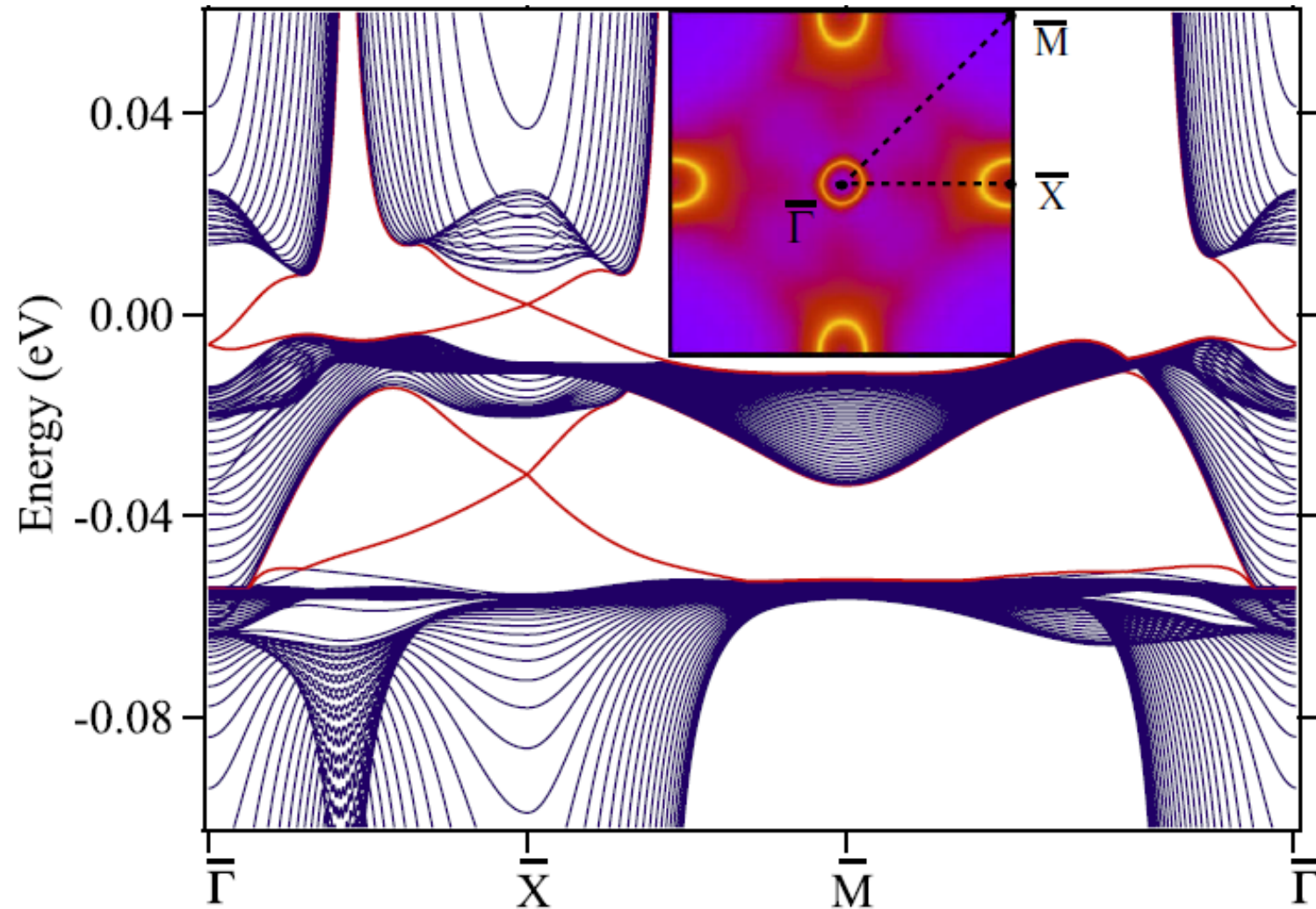
M. Dzero *et al.*, PRB **85**, 045130 (2012).

H. Miyazaki *et al.*, PRB **86**, 075105 (2012).

T. Takimoto *et al.*, J. Phys. Soc. Jpn. **80**, 123710 (2011).

SmB₆: A candidate 3D topological Kondo insulator

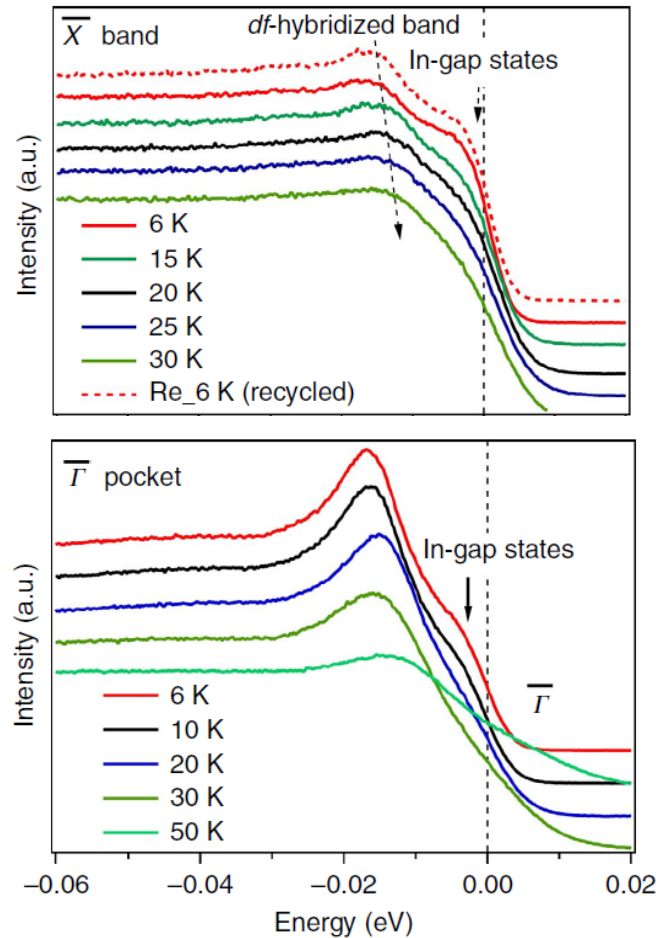
LDA + Gutzwiller calculation



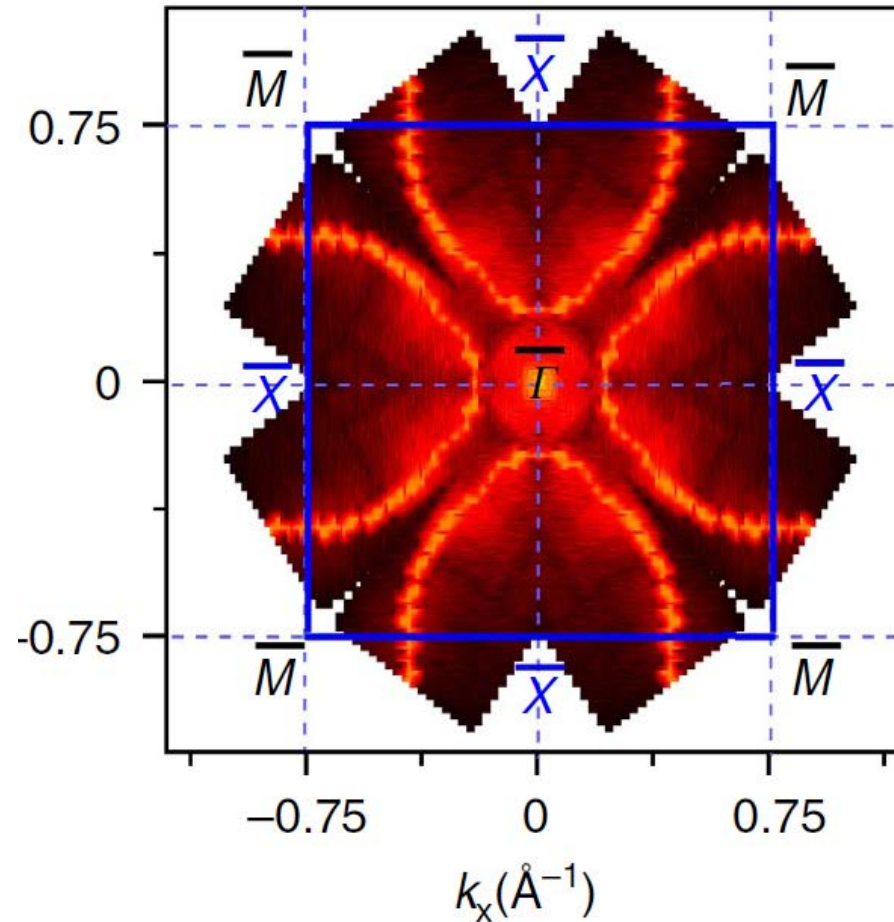
SmB₆: A candidate 3D topological Kondo insulator

$\Delta E = 5$ meV, $T = 7$ K

Neupane et al., Nat. Comm. **4**, 2991 (2013)



Topology of Fermi surface



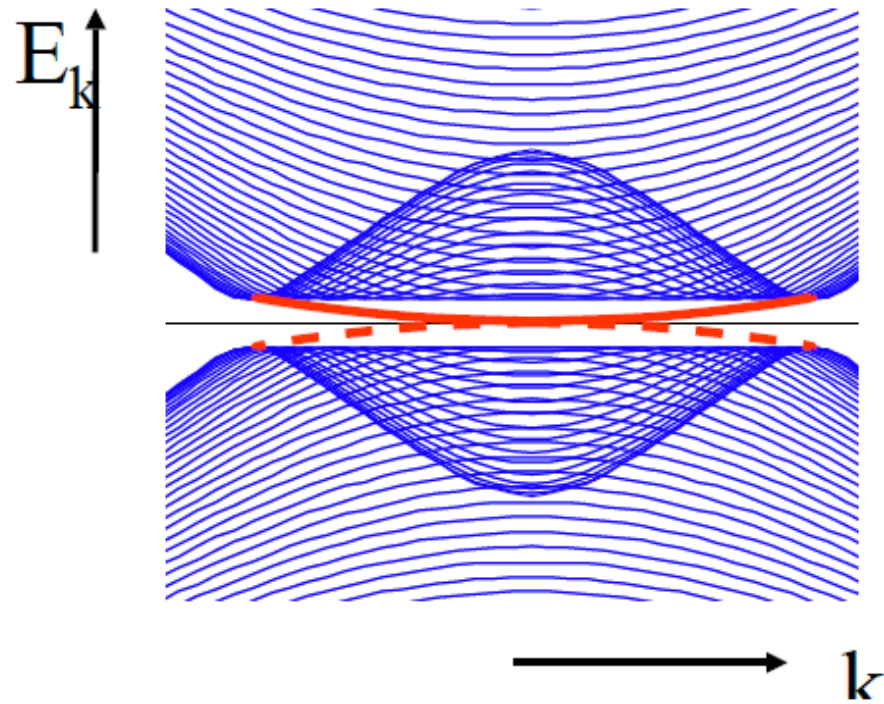
Jiang et al., Nat. Comm. **4**, 3010 (2013)

Frantzeskakis et al., Phys. Rev. X **3**, 041024 (2013)

Xu et al., PRB **88**, 121102(R) (2013)

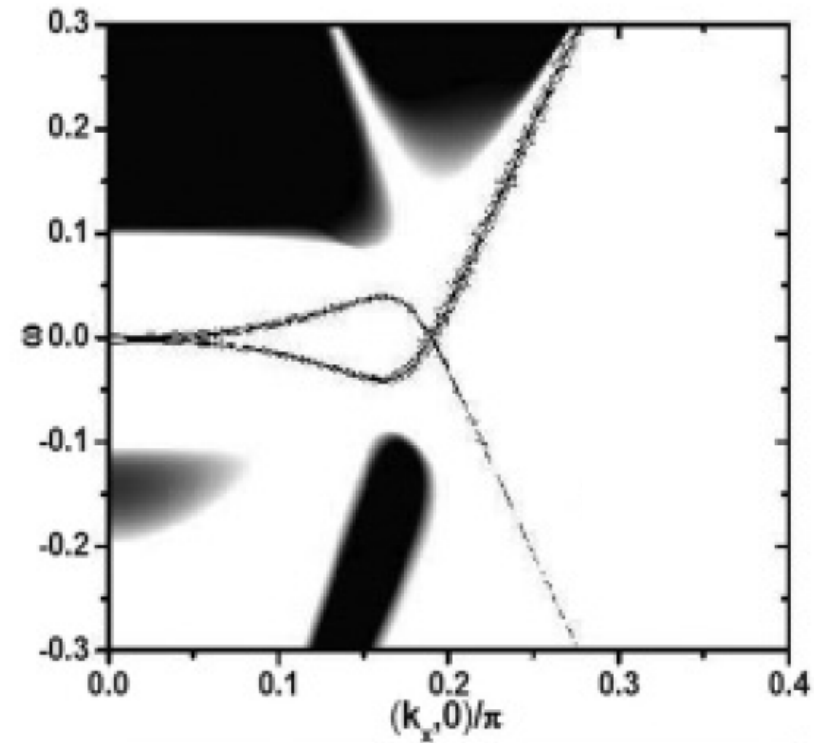
Superconducting topological insulators - $\text{Cu}_x\text{Bi}_2\text{Se}_3$

Fu & Berg, PRL **105**, 097001 (2010).



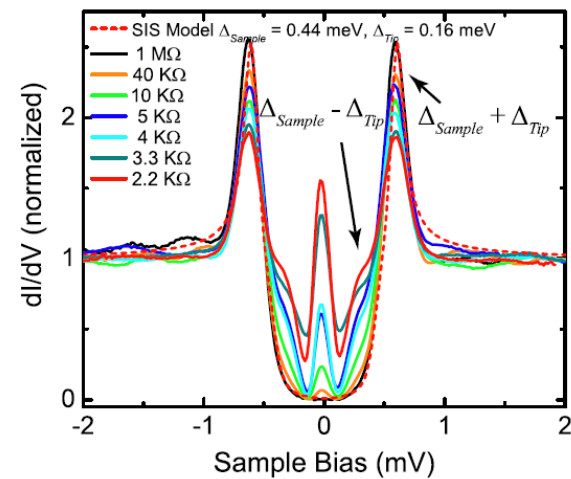
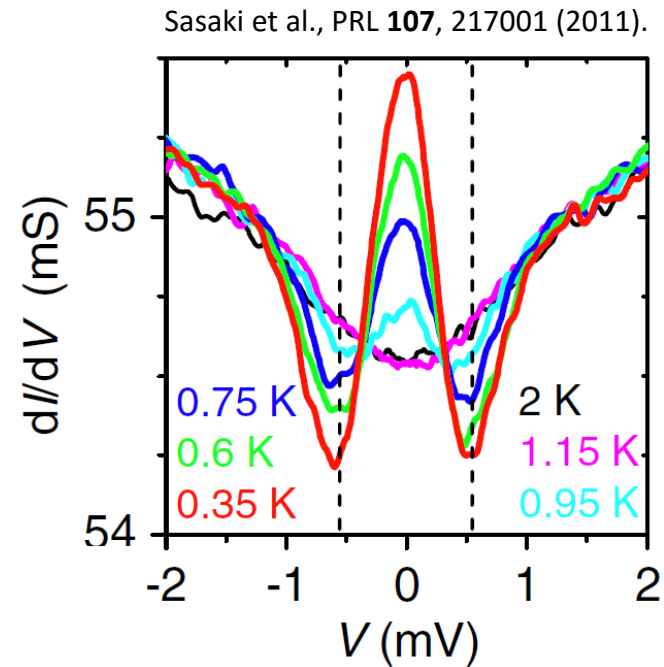
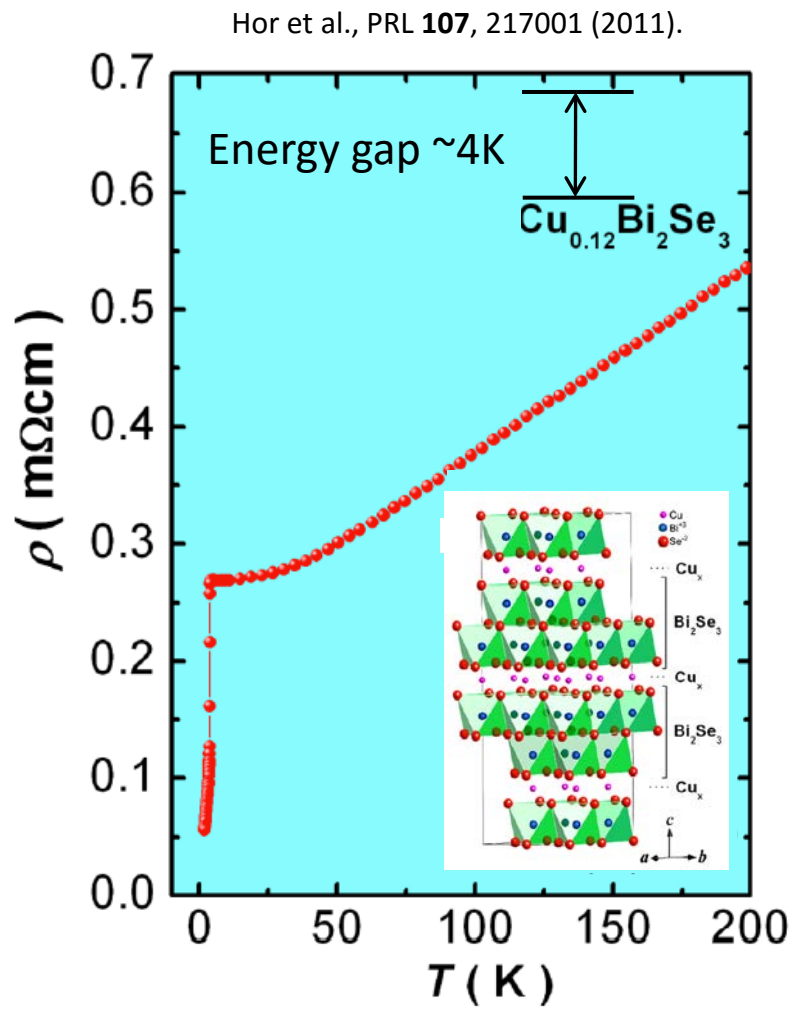
Calculated electronic structure

Hao & Ng, PRB **83**, 134516 (2011).



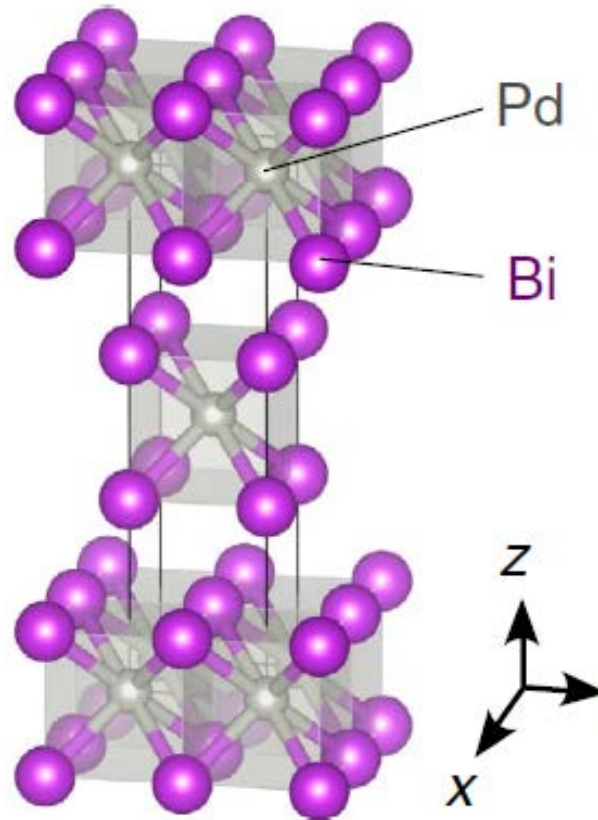
Calculated ARPES intensity

$\text{Cu}_x\text{Bi}_2\text{Se}_3$

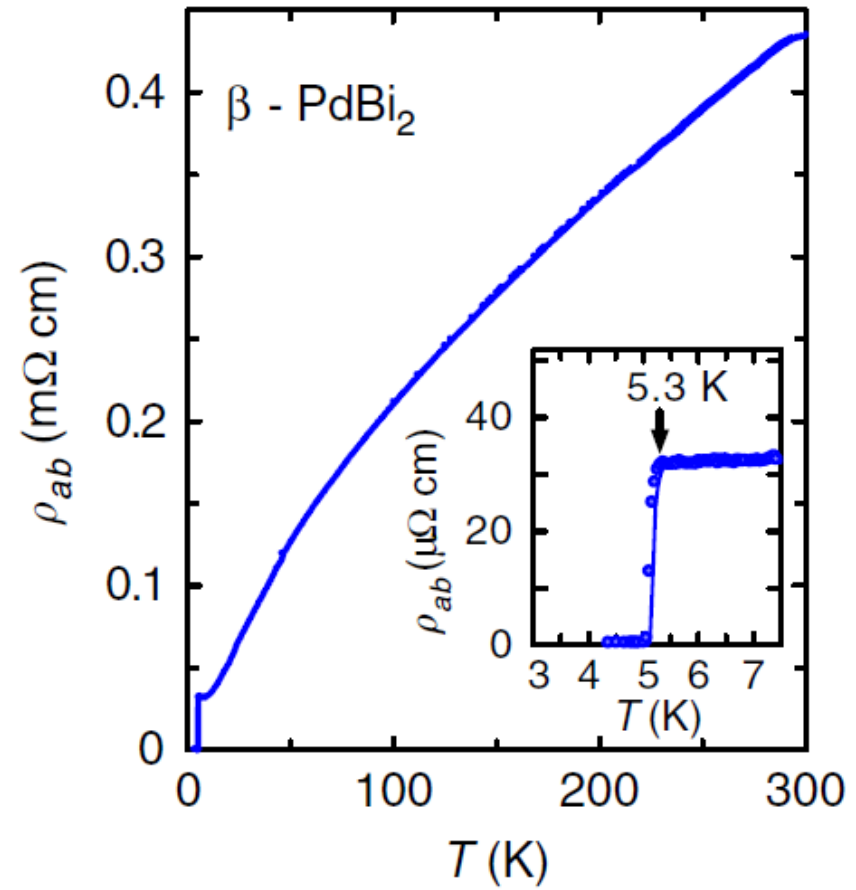


Levy et al., PRL **110**, 117001 (2013).

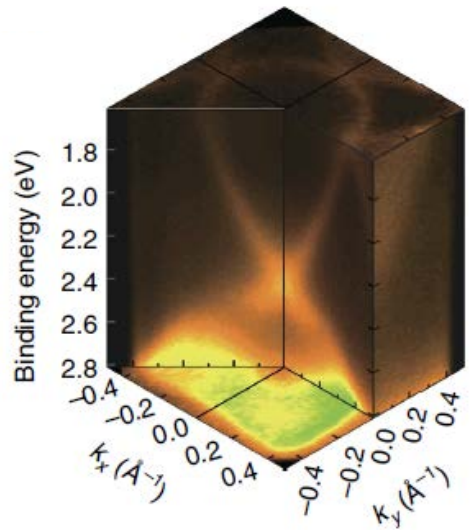
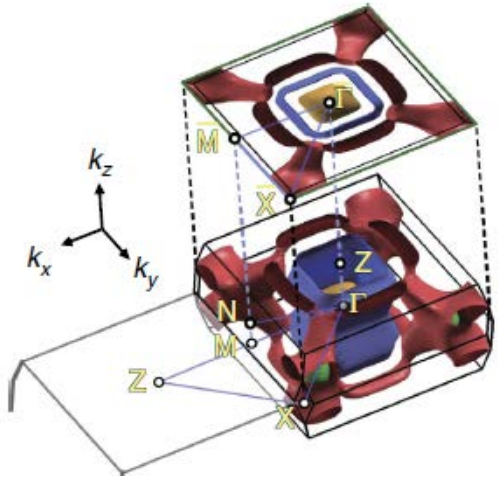
β -PdBi₂



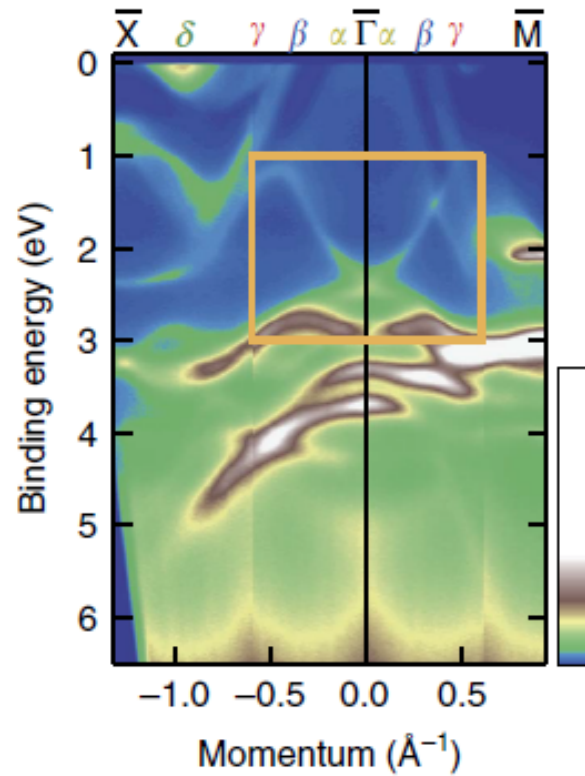
van der Waals bonded
between PdBi₂ layers



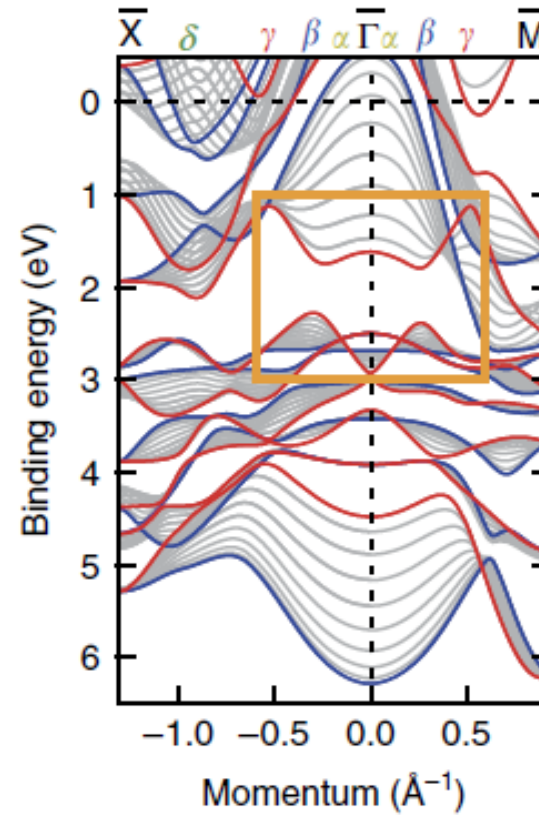
β -PdBi₂



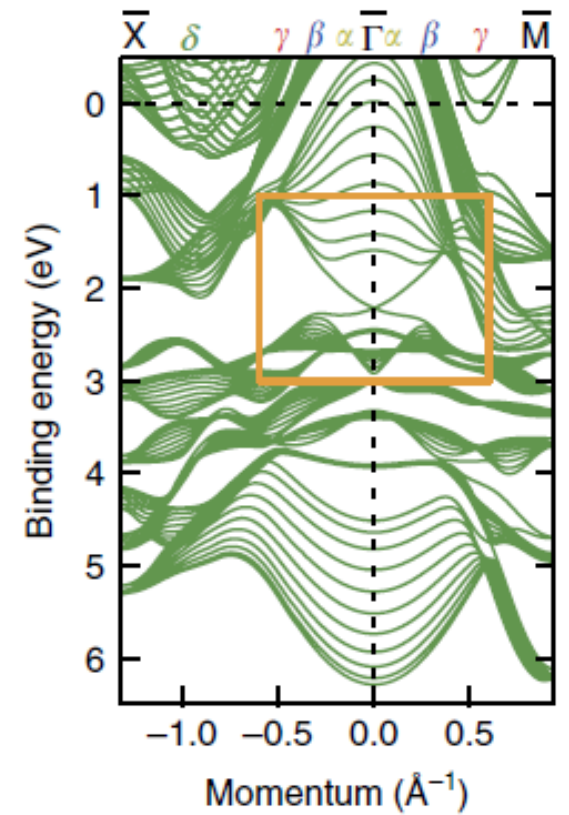
ARPES



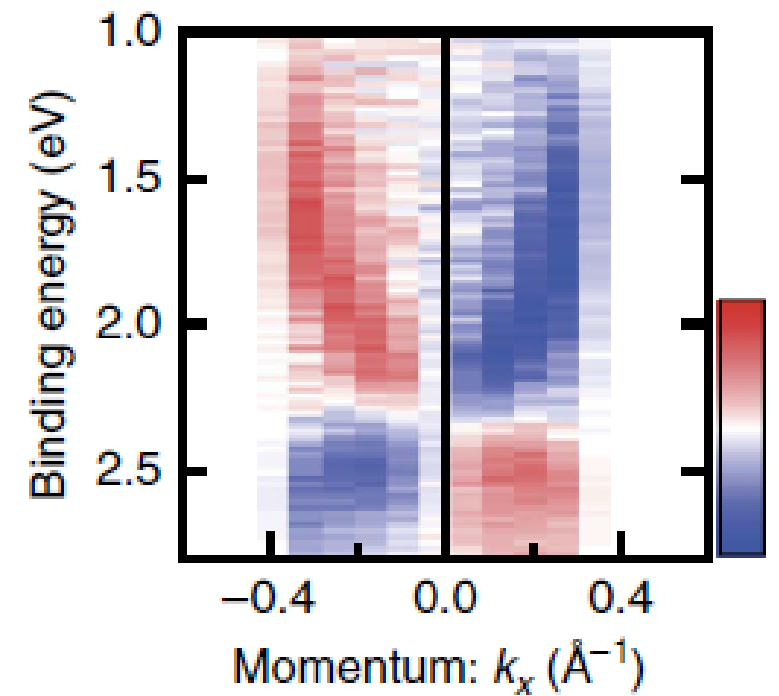
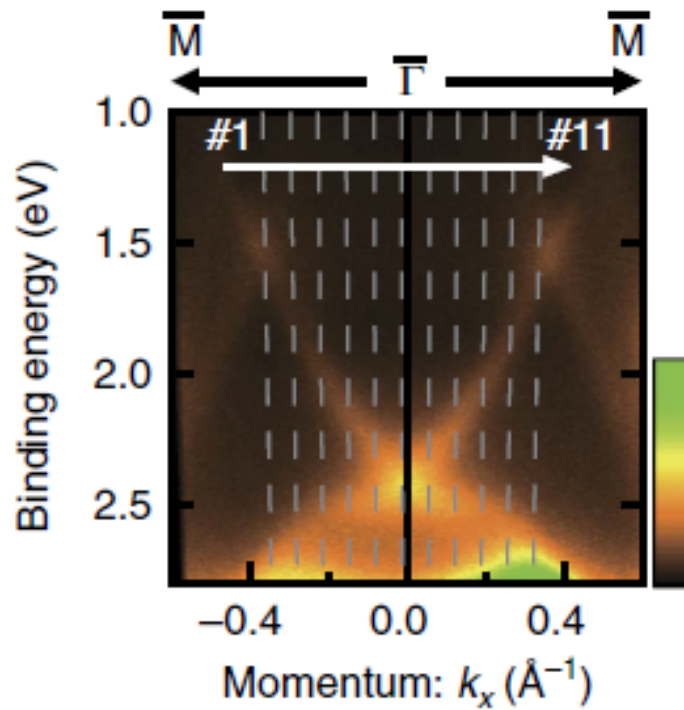
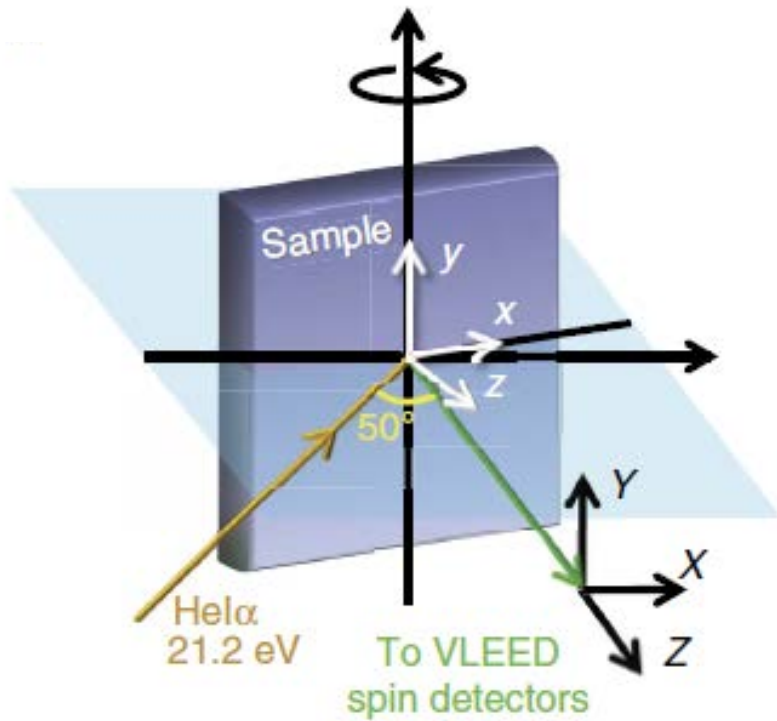
LDA projected bulk



11-layer slab calculation



β -PdBi₂

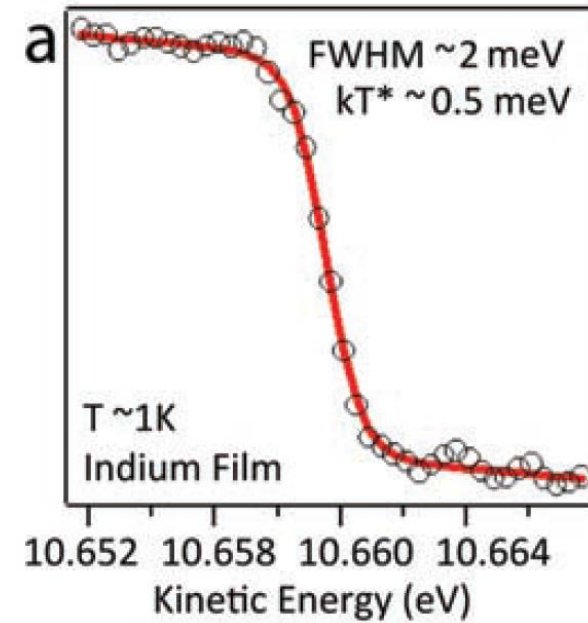
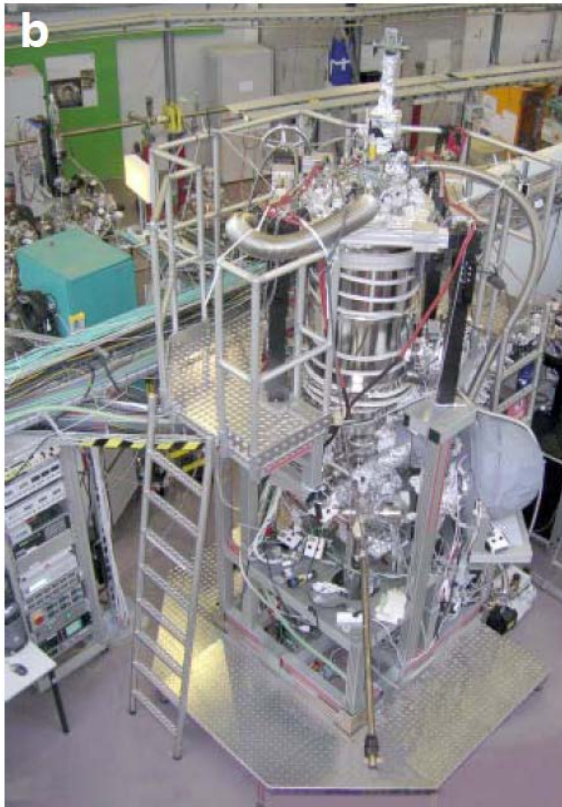


Towards ultra-low temperature + high-resolution ARPES

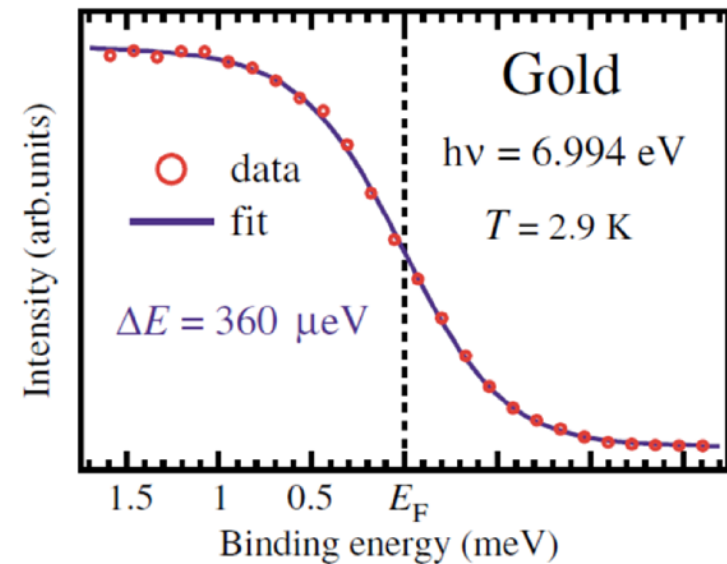
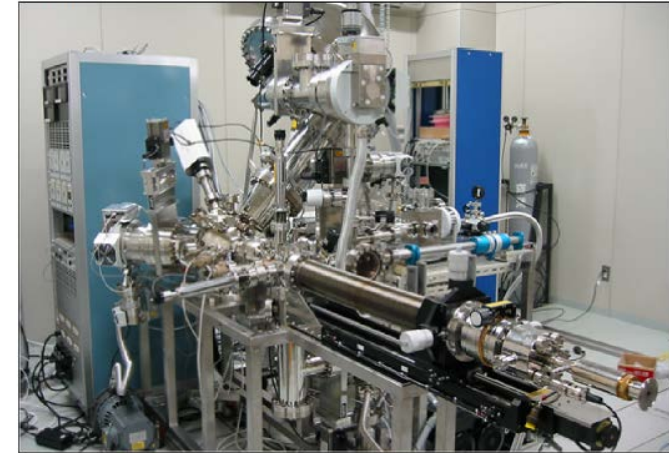
Ultrahigh resolution (Shin Lab; ISSP Tokyo)

Shimojima et al., JPSJ **84**, 072001 (2015)

Ultralow temperature (1^3 beamline @ BESSY II)



$$\sqrt{1^2 \text{ meV} + 1^2 \text{ K} + 1^2 \text{ meV}} \rightarrow \text{FWHM } 1.46 \text{ meV}$$
$$kT^* \sim 0.36 \text{ meV}$$



Conclusions

